#### 8085-BASED UNIVERSAL EPRON PROGRAMMER

BY

#### KHANDAKER ATWAR HOSSAIN

#### A PROJECT REPORT

SUBMITTED TO THE DEPARTMENT OF ELECTRICAL AND ELECTRONIC ENGINEERING, BANGLADESH UNIVERSITY OF ENGINEERING AND TECHNOLOGY IN PARTIAL FULFILMENT OF THE REQUIREMENT FOR THE

DEGREE OF

MASTER OF ENGINEERING



DEPARTMENT OF ELECTRICAL AND ELECTRONIC ENGINEERING
BANGLADESH UNIVERSITY OF ENGINEERING AND TECHNOLOGY

JANUARY, 1985.



#### CERTIFICATE

This is to certify that this project work was done by me and it has not been submitted elsewhere for the award of any degree or diploma.

Countersigned

(Dr. Syed Mahbubur Rahman) Supervisor.

Signature of candidate

Accepted as satisfactory for the partial fulfilment of the requirements for the degree of Master of Engineering in Electrical and Electronic Engineering.

#### EXAMINERS

1. (Dr. Syed Mahbubur Rahman)
Assistant Professor,
Computer Engineering Department
Bangladesh University of Engineering
and Technology, Dhaka, Bangladesh

Supervisor

2. (Dr. Shamsuddin Ahmed)
Dean
Faculty of Electrical and
Electronic Engineering,
Bangladesh University of Engineering
and Technology, Dhaka, Bangladesh

Member

3. (Dr. Syed Fazl-i Rahman)
Professor and Head,
Department of Electrical and
Electronic Engineering,
Bangladesh University of Engineering
and Technology, Dhaka, Bangladesh

Member

4. (Dr. Mahfuzur Rahman)
Professor and Head,
Computer Engineering Department
Bangladesh University of Engineering
and Technology, Dhaka, Bangladesh.

Member



DHAKA

JANUARY, 1985

# ALL PRAISES TO ALLAH, THE MERCIFUL

#### ACKNOWLEDGEMENT

The author expresses his indebtness and deep sense of gratitude to Dr. Syed Mahbubur Rahman, Assistant Professor of Computer Engineering Department, Bangladesh University of Engineering and Technology, Dhaka for his continuous guidance encouragement and help and continuous suggestions all along the course of this work.

The author wishes to express his great indebtness to Dr.

Shamsuddin Ahmed, Dean of the Faculty of Electrical and Electronic

Engineering for his interest in progressing the project work.

The author also expresses his greatfulness and thanks to Dr. S.F. Rahman, Head of the Department of Electrical and Electronic Engineering and to Dr. Mahfuzur Rahman, Head of the Department of Computer Engineering, who were kind enough to provide all the facilities of the Departments for this work.

The author expresses his indeptness to Mr. Abdul Hannan, Principal, Khulna Engineering College, for his keen interest and encouragement in pursuing the post graduate studies.

Microprocesser based designs require to store their eperating and additional programs in a permanent memory such as an EPROM. EPROM programmers are thus an essential requirement for any microprocessor based design. The present project work deals with the development of a 8085-based EPROM programmer, which can be used in Program, Verify, Read, Display, Copy and Frint Mode. Programs have been developed for the Intel 2716, 2732, 2764 and 27128 EPROMs. Since the programmer is software controlled, any type of EPROM can be programmed just with a little change in the control program of the EPROM programmer. The project work, besides, greatly encouraging microcomputer based designs, will also save buying of costly manufactured programmers available in foreign market.

# CONTENTS

CHAPTER	l I	INTRODUCTION		Page
	1.1			
			•••	1
	1.2	Non-volatile memory	• • •	1
	1.3	Some available EPROM	•••	2
	14	Aim of the project		3
CHAPTER	II	SEMICONDUCTOR MEMORY		
	2.1	Read-only memory		5
		2.1.1 Manufacture-programmed ROM characteristics	• • •	6
		2.1.2 Programmable read-only memo programming characteristics	ry	8
		2.1.3 Erasable programmable Read- memory (EPROM) programming	only	
		characteristics	• • • •	11
	2.2	Erasure characteristics of the EPR	MC	14
CHAPTER	III	MICROCOMPUTER		
	3.1	Basic microcomputer organization		17
	3.2	The Intel 8085 microprocessor		19
		3.2.1 8085 architecture and its pin diagram		19
CHAPTER	IV	INTERFACE WITH PERIPHERAL DEVICE		24
CHAPTER	V	PROGRAMMING CHARACTERISTICS OF INTERPROMS	EL	
	5.1/	Comparative study of Intel EPROMs		28
	5.2	27-series EPROM operation		29
		5.2.1 Read mode		30
		5.2.2 Standby mode		30
		5.2.3 Program inhibit mode		33
		5.2.4 Program verify mode		33
		5.2.5 Programming mode		77

# CONTENTS (Contd.)

CHAPTER			Page
5.3	Programming of 8-48 and 8748 EPROMs		34
CHAPTER	VI HARDWARE DESIGN OF EPROM PROGRAMMER		
6.1	Functional description of EPROM program	mer	38
6.2	Detail circuit diagram of the programme	r	40
	6.2.1 Address decoder		40
	6.2.2 I/O and Expansion buffer		44
	6.2.3 Address high and address low buff	er	45
	6.2.4 The data latches	•••	45
*	6.2.5 Control latches	•••	46
6.3	Connection of KPROM pins	• • •	49
CHAPTER	VII SOFTWARE DEVELOPMENT		
7.1	Function of the programmer	•••	52
7.2	Program development of the programmer		53
	7.2.1 Read sub program		55
	7.2.2 Conversion of ASCII coded number to hexadecimal number	•••	58
	7.2.3 MOVE Subprogram		64
	7.2.4 DISPLAY Subprogram		65
	7.2.5 VERIFY Subprogram		68
	7.2.6 PROGRAM Subprogram		71
	7.2.7 COPY Subprogram		75
	7.2.8 PRINT Subprogram	•••	79
CHAFTER	VIII DISCUSSION AND CONCLUSION		
	REFERENCES		
	APPENDIX - A		

Complete software program

## APPENDIX - B

- I. Pin diagram of IC Chips
- II. Pin diagrams of EPROMS.
- III. Programming waveforms of EPROM

## APPENDIX - C

I. Printed circuit board design

#### CHAPTER - I

#### INTRODUCTION



#### 1.1 General Introduction

The advent of discrete semiconductors and the technological follow-on, e.g., the monolithic integrated circuits, have had significant impact on the performance, cost, reliability, maintainability, physical size, and architecture of central processing units of digital computer and allvarieties of digital systems.

The use of semiconductors has now started to spread to peripheral equipment and memory. When the memory elements are organized and combined in a particular arrangement, they are referred to as memory system.

# 1.2 Non-Volatile Memories

A memory section for storing permanent data, e.g., list of constants, tables of data conversion like trisonometric sine tables etc., and fixed computer programs like operating instructions, editor, monitor or utility programs, subroutins, keyboard encoder, character generator etc., do not require a write capability once it is loaded; thus time and cost may be saved by omitting the write feature. Such a storage device is called a Read-only Memory or ROM. The information stored in these devices will remain unchanged even if power is removed from the system which offers a considerable convenience. Moreover for data only occassionally changed, there are even cases between full write capability and the ROM. One such type is erasable programmable read-only memory

or EPROM.

EPROM has quickly found its popularity as a non-volatile temporary storage medium. More likely responsible is its attractive combination of field programmability, high density, and low power consumption when compared to bipolar fusible-link memories. Such devices, built with either p- or n- channel metal-oxide-semiconductor technology, have served well in prototyping microprocessor based system. There is an extra advantage for the user to see the actual silicon chip through the quartz window that lets the ultraviolet light for erasure.

## 1.3 Some Available EPROM Programmers

To program the EPROMs some devices are required known as EPROM programmer. Various types of EPROM programmer are available in the market. Performance of these programmers varies with the cost. These programmers are sometimes ON-line connected with the computer and sometimes independent units. Some available programmers are listed below along with their approximate prices.

- i. "Universal PROM programmer" by Intel corporation. It can program all kinds of EPROMs using different personality cards and programming adapter socket. It can be used as an independent unit and also micro-computer based with RS-232 cable. Price is around £ 1000.
  - ii."PROM Programmer M9807" by Pro-Log Corporation. They

state "Built to handle the Programmable devices of today .... and tomorrow". Cost is above £ 1000.

iii. "EPROM Emulator and Programmer EP4000 produced by G.P. Industrial Electronics Ltd. It is a microprocessor controlled programmer which can program all the popular EPROMs of Intel Corporation. Cost is about £ 600.

iv. Rockwell International introduced an EPROM programmer with their microcomputer AIM-65<sup>9</sup>. It can program only the Intel 2716 EPROM. Duplication is not possible here.

v. H. Muller (Switzerland) designed an EFROM Programmer for the popular 2716 & 2732 EPROMs using timer, logic gate and other accessories. There is no scope of duplication. Material cost is around £  $25^{10}$ .

vi. H.S.Lynes (England) designed an EPROM Programmer to accommodate 2708, 2716 & 2732 EPROMs using drivers, latches etc. It is to be interfaced with microcomputer. Material cost is around £  $20^{11}$ .

## 1.4 Aim of the Project:

The EPROM Programmer to be designed is microcomputer controlled. It can be used for programming Intel 2716, 2732, and 2764 and 27128 EPROM and the EPROMs within the 8048H & 8087H microcomputer chips. An additional advantage over the available EPROM programmers is that with little modification

it can be used to program any type of EPROM available in the market. The 40 output ports should be connected to proper pins of the EPROM and a software with a little change should be written for the particular EPROM to be programmed.

EPROM is an essential part in all microcomputer based designs. As such the design of such a flexible EPROM programmer will greatly help the research works on the microcomputer designs. It will also replace the need for investment of quite a large amount of foreign exchange required for this purpose. With industrial backup commercial manufacturing may also be taken up.

# CHAPTER - II

#### SEMICONDUCTOR MEMORY

#### 2.1 Read-Only Memory

Semiconductor memories fall into two basic categories.

Read-only memories (ROMs) and Randam-access read/write memories (RAMs). ROM forms an important part of memory requirement in most microcomputer systems. This type of memory are also called fixed memory, permanent memory or read-only store (ROS).

In principle it is simply a special combination circuit because an input signal combination (address and entry) defines a unique output combination. The ROM can take a digital code at its input terminals and provide a unique digital code on its output terminals. The relationship between its input and output codes are relatively fixed, usually alterable only by slow techniques, and for this reason it is termed "read-only". The difference between read-only memory and read/write memory is the level of difficulty in changing the stored information.

The ROM, being a fixed memory, is non-volatile: i.e., loss of power or system malfunction does not change the contents of memory. The ROMs have the feature of random access, which means that the access time for a given memory location is the same as that for all other locations.

As a result of the recent advances in IC technology, ROMs exist in many forms. The technique employed for storing information in the ROM (called programming) provides a convenient method for classifying all ROMs into one of the following three

# categories4.

- 1. Programmed during manufacture
- 2. One-time programmable after manufacture by the user
- Programmable after manufacture with provision for erasing and reprogramming.

Provision for programming any of these three types commonly involves some sort of link, which may be opened or closed, between each row-select line and an input line of each OR gate. These units are then specified according to the information pattern that is to be programmed into the unit in a manner that depends upon the units type.

# 2.1.1 Manufacture-Programmed Read-Only Memory (ROM): Programming Characteristics.

ROMs are programmed usually as one of the final steps of their manufacture. The links are simply gaps that may be bridged by a final metalization pattern that is placed onto the circut according to the desired information to be programmed. This is done with a mask that determines the precise pattern, which is custom-made for a particular application. The mask is expensive to make but may be used to program any number of units. So this type of ROM is best suited for mass production.

An example of this first type of ROM unit using pn junction devices is shown in Fig.2.1. A diode is provided for each bit location in the unit. As can be seen a gap occurs in each path between a diode and the common line for a column. A value of "O"

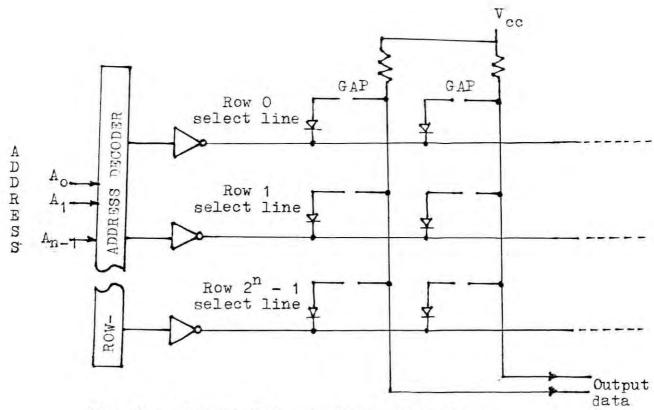


Fig. 2.1 Circuit for a mask-programmed pn junction read-only memory unit.

is programmed into a particular bit position by bridging the corresponding gap, otherwise, the value of that bit is 1.

From the figure 2.1 it can be noticed that the common line of a column is normally pulled high by a resistor and that only the select line corresponding to the specified address can pull it low. If the gap to the diode connected to that select line is left open, then the common line remains high, corresponding to an output of "1". If the gap is closed on the otherhand, then the common line is pulled low by the select line, corresponding to an output of "0".

# 2.1.2 Programmable Read-Only Memory (PROM): Programming Characteristics

This type of ROM can be programmed one time by the user. It has generally a link that, after manufacture, can be altered one way, either from closed to open or vice verse. The most common way of doing this is to make the link from a fusible metal, such as NiCr, which can be selectively "blown" (i.e., open circuited) by supplying an external current of sufficient magnitude. An example of such a ROM unit is shown in Figure 2.2. The unit is similar to the previous example of a pn junction ROM unit, except that NiCr fuses are placed across the gaps and that there is provision for each of these fuses to be blown.

There are two modes of operation for this type of ROM:

- i. Read mode
- ii. Program mode

The mode at any time is determined by the value of the power-supply voltage  $V_{\rm cc}$ . For the read mode,  $V_{\rm cc}$  is placed at its normal value (e.g., 5 V); for the program mode,  $V_{\rm cc}$  is raised to higher voltage (e.g., 10 V). A threshold circuit is connected to  $V_{\rm cc}$  to generate the signal labled "Read Mode" which is logic-1 when the ROM unit is in the read mode of operation. This signal, Read Mode, is used in conjunction with an external signal, Chip Enable, to affect both the enabling of the row-select lines and the enabling of the output data lines.

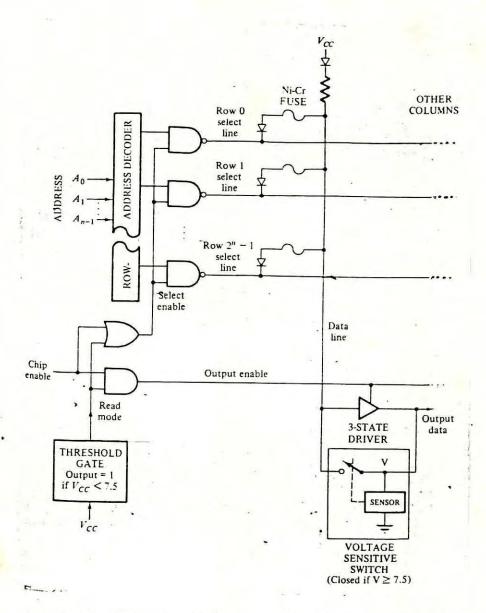


Fig. 2.2 Circuit for a fusble-link programmable readonly memory unit.

Read mode: In this mode the row-select lines behave presisely the same way as in the preceding example of a pn junction ROM.

As can be seen in Fig. 2.2, NAND gates are inserted into the row-select lines. The second input line of each of these NAND gates, which is driven by the OR of Chip Enable and the signal Read Mode, will be at logic-1, since Read Mode is at logic-1. In this case the NAND gates simply invert the decoder outputs. The row-select line corresponding to the specified address is at logic-0, and all other row-select lines are at logic-1.

If the fuse is intact for a column and the selected row.

then the data line for that column is forced low (logic-0);

otherwise, the data line is pulled high (logic-1) by the pull-up

resistor. A 3-state driver is used to couple each column data

line to an overall output line labelled "Output Data". These

3-state drivers are controlled by a signal labeled "Output Enable",

which is the AND of Chip Enable and the signal Read Mode.

Program mode:- In this mode of operation, V<sub>cc</sub> is raised to a higher voltage (e.g., IOV). This affects the circuit in several ways. It causes the signal read mode to go to logic-O, which has two effects. First, the signal Select Enable is made to depend upon the external signal Chip Enable, thereby making the row-select line corresponding to the specified address to be logic-O only if Chip Enable is logic-1. Second, it causes the signal Output Enable to be logic-O, which disables the 3-state output drivers independent, of the value of Chip Enable. In addition

and most important, the row-select lines that do not correspond to the specified address are raised to higher voltage (e.g. 10V), since the gates that drive them use the power-supply voltage  $V_{\rm cc}$  to determine the logic-1 voltage level.

To cause a fuse to be blown, the desired address is specified, the Chip Enable line is then activated to enable the row-select lines, and then a specified current (approximately 50mA) is supplied from a current source to the appropriate Output Data line. This current passes through a voltage-sensitive switch to the data line of the corresponding column. The switch is a special circuit that closes when the voltage V applied by the current source exceeds a value somewhat higher than the maximum logic-1 level of 5V. The applied voltage will be sufficiently high if the specified current is made to flow. Once past the switch, the applied current flows through the fuse and diode that are connected to the row-select line that is low (logic-0). All other row-select lines are at approximately 10V and therefore draw an insignificant amount of applied current. After a short time the current causes the fuse to melt away. When a sufficient time has passed to allow for this, the Chip Enable line is deactivated. The process may then be repeated for other fuses that are to be blown in the same row and then for other rows. J

# 2.1.3 <u>Erasable Programmable Read-Only Memory (EPROM):</u> <u>Programming Characteristics.</u>

The third type of read-only memory unit, which can be programmed, erased, and reprogrammed, is refferred to as "erasable

programmable read-only memory" or in short EPROM. This type of unit generally makes use of a link that can be placed on one condition (say closed) on a selective basis and into the other condition (say open) on a collective basis. Programming such a unit consists of first placing all links collectively into a specific condition, which amounts to erasing any previous information content, and then placing desired links into the opposite state, one at a time.

A notable example of a link that is used in EPROM units consists of a special type of MOS transistor having what is called a floating gate. A specific form of such a transistor is that of a p-channel normally-off (enhancement-mode) MOS transistor with its gate electrode surrounded by insulation, as shown is Fig.2.3.

The gate has no lead attached to it but may, however, be made to acquire a negative charge, as will be seen. When charged negatively, the gate induces a positive charge into the channel, just as it would if a negative potential with respect to the substrate were applied to the gate. With a positive charge in the channel the transistor is conductive. On the otherhand, if the gate has no regative charge, then no positive charge is induced into the channel and the transistor is not conductive.

Negative charge is supplied to the gate by injecting electrons from the drain through the insulation to the gate. This is done by applying a relatively high positive voltage to the source with respect to the drain.

The resulting electric field induces a relatively high positive voltage on the gate with respect to the drain.

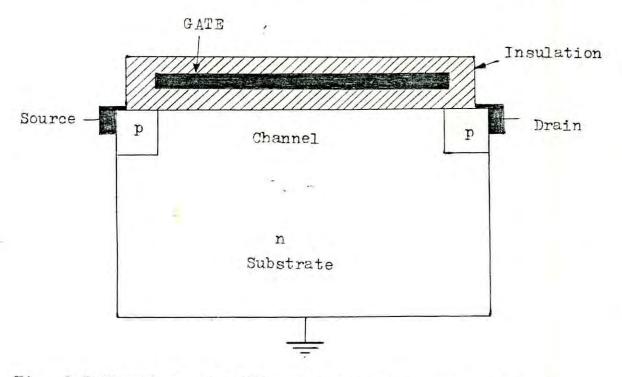


Fig. 2.3 Floating-gate PMOS enhancement-mode transistor for EPROM units.

Roughly speaking, this voltage causes a breakdown to occur at the junction between the drain and the insulation, resulting in a flow of rather energetic electrons from the drain into the insulation. Owing to their energetic state, the electrons are able to drift through the insulation to the gate electrode. This electron charge on the gate will remain there almost indefinitely unless specifically removed. Charge is removed from the gate by irradiating the area with ultraviolet light, which imparts sufficient energy to each electron to bring it into a conductive energy band in the insulation. The electrons are then able to flow away from the gate owing to their mutual repulsion.

A read-only memory unit using these special transistors can be structured in a manner similar to the previous example of a MOSROM, which was shown in Fig. 2.1. In this case, each gap in the unit is bridged with one of these floating-gate transistors. In addition, circuitry is included that allows each floating-gate transistor to be selected for application of the necessary voltage to charge the gate. This selection process involves the address and output-data lines.

To program the resulting EPROM, all links are first opened (corresponding to logic-1) by irradiating the unit with ultraviolet light of sufficient intensity and duration. Then, for those bit positions that are to contain logic-0, the corresponding links are closed one at a time.

# 2.2 Erasure Characteristics of the EPROMs

The erasure characteristics of the Intel 27-series EPROMs and the EPROMs within the 8748 & 8048 micro-computer chips are such that erasure begins to occur when exposed to light with wave lengths shorter than approximately 4000 Angstrom (%). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000-4000 % range. Data show that constant exposure to room level fluorescent lighting could erase the typical EPROMs approximately in 3 years while it would take approximately one week to cause erasure when exposed to direct sunlight. If the EPROMs are to be exposed to these types of lighting conditions for extented periods of time, opaque labels

are available which should be placed over the chip window to prevent unintentional erasure.

The recommended erasure procedure for the EPROMs is exposure to shortwave ultraviolet lightwhich has a wavelength of 2537%. The integrated dose (i.e., UV intensity X exposure time) for erasure should be a minimum of 15 w-sec/cm². The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with a 12,000 MV/cm² power rating. The chip should be placed within one inch of the lamp tubes during erasure. Some lamps have a filter on their tubes which should be removed before erasure<sup>5</sup>.

# CHAFTER - III

#### MICROCOMPUTER

#### 3.1 Basic Microcomputer Organization

A microcomputer is a bus-oriented system of subassemblies that are implemented utilizing the technology of LSI. Functions of these subassemblies provide for manipulation of information, ordering the sequence of instruction execution, interpretation of instructions, control and timing of bus operation, storage of instructions and data, and communication between the computer and the external environment. The first four of these functions are frequently handled by a single subassembly known as a microprocessor. The storage function is handled by a memory subassembly. This subassembly may consists of ROM and/or RAM. The external communication is performed by a set of subassemblies known as input and output ports. Each port provides an interface between the microprocessor and some external device.

Figure 3.1 shows the general layout of a microcomputer and Fig.3.2 shows the basic blocks of an 8-bit microcomputer system. The various bases which connect these blocks are also shown. There are three buses:-

- 1. The address bus
- 2. The data bus
- 3. The control bus

These buses connect the microprocessor (CPU) to each of the ROM, RAM and I/O elements so that information transfer between the microprocessor and any of the other elements can take place.

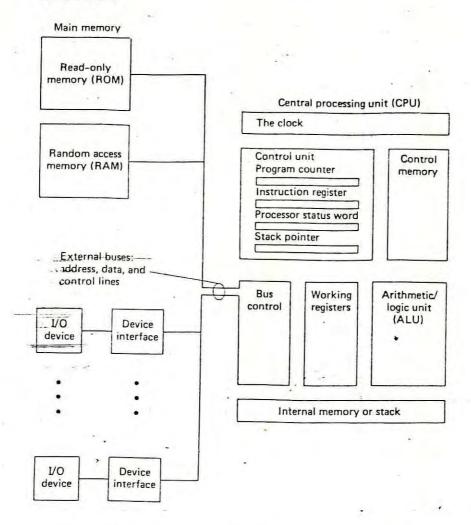


Fig. 3.1 General layout of a microcomputer.

Note: The I/O device may be the Keyboard (Input), video display (Output), EPROM Programmer (Output).

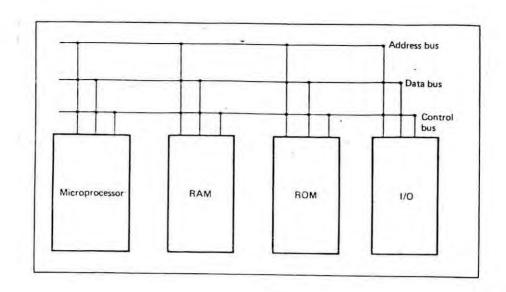


Fig. 3.2 Block Diagram of a Typical Microcomputer

Address bus is used for transferring information from microprocessor to memory or I/O elements in one direction only. When the microprocessor wants to transfer information between itself and a certain memory location or I/O device, it generates the 16-bit address from an internal register on its 16 address pins  $A_O$  -  $A_{15}$ , which then appears on the address bus. These 16 address bits are then decoded to determine the desired memory location or I/O device. The decoding process normally requires hardware (decoder).

The data bus is a bidirectional bus. In 8085 microprocessor, the 8 data pins are used to sand lower 8 address bits in addition to data. That is the data pins are time-shared or multiplexed. When address bits are sent the address latch enable (ALE) pin becomes HIGH.

The control bus consists of a number of signals that are used to synchronize the operation of the individual micro-computer element. The microprocessor sands some of these signals to the other elements to indicate the type of operation being performed.

### 3.2 The Intel 8085 Microprocessor

The Microprocessor is the CPU of the microcomputer and is the combination of control unit and arithmatic and logic units. Therefore, the power of the microcomputer is determined by the capabilities of the microprocessor and its clock frequency determines the speed of the microcomputers. Microprocessor consists of logical components that enable it to function as a programmable logic processor. Some of the components, i.e., the program counter, stack and instruction register, provide for the management of a program. Other components, i.e., the ALU, Carry flip-flop, scratchpad register and data-address register provide for the manipulation of data. The remaining components, i.e., the decoder, timing and control unit specify and coordinate the operation of the other components. Internal pathways interconnect the components to provide for transferring data between designeated components. Connection of the microprocessor to other units (memory and I/O devices) is done with the address, data, and control buses.

## 3.2.1 The 8085 Architecture and its Pin Function

Intel 8085 8-bit microprocessor is housed in a 40-pin dual-in-line (DIP) package. Fig. 3.3 shows the Intel 8085

pin diagram and Fig. 3.4 shows the functional block diagram of the Intel 8085 microprocessor.

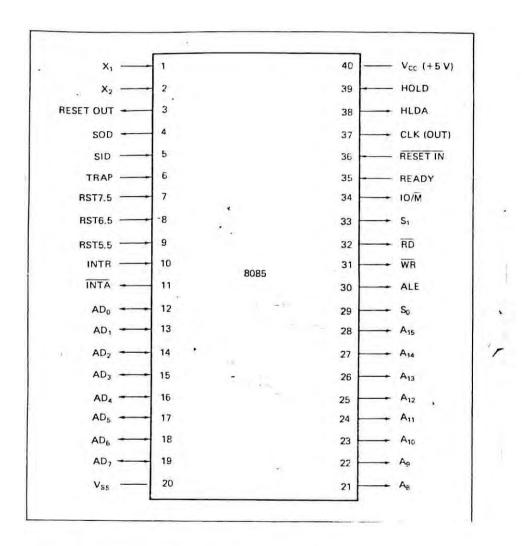


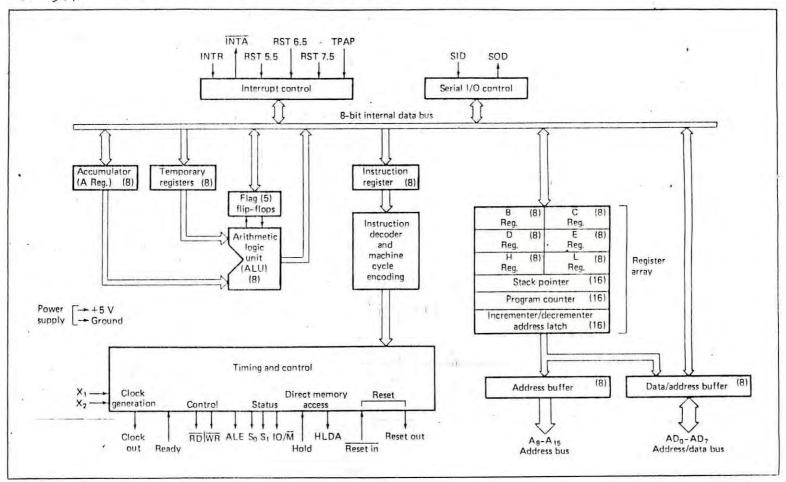
Fig. 3.3 Microprocessor signals and Pin Assignments

The internal organization or architecture of the Intel 8085 microprocessor is briefly discussed below.

It has a 16-bit program counter and address latch which

Figure 3.4 8085 Microprocessor Functional Block Diagram (Courtesy of Intel Corporation)

11



feed the dedicated address bus  $(A_{15} - A_8)$  and the dual purpose address/data bus  $(AD_7 - AD_0)$ . Parallel data enters and leaves the MPU via the multiplexed address/data bus  $(AD_7 - AD_0)$ . The address/data bus transmits an address when the ALE control line is HIGH and data when the ALE line is LOW.

The 8-bit internal data bus carries input or output data throughout the unit. The data can flow from the internal data bus to the 8-bit accumulator or temporary register, flags, instruction register, interrupt control unit, serial I/O control unit, any of the general purpose registers (B,C,D,E,H and I), 16-bit stack pointer, 16-bit program counter, or 8-bit data/address buffer. The arithmetic-logic unit (ALU) is being fed by two 8-bit registers (accumulator and temporary register). The flag flip-flops have five status indicator as shown in Fig. 3.5. below.

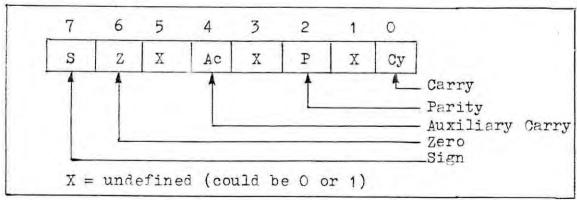


Fig. 3.5 Format of Processor Status Word

The instruction register feeds the instruction decoder.

This instruction decoder interprets the current instruction and determines the microprogram to be followed or the machine

cycle encoding. The instruction decoder then instructs the timing and control section as to the sequence of events to be followed. The timing and control section coordinates actions of both processor and the peripheral.

The RD pin signal is outputted LOW during a memory or I/O READ operation. Similarly, the WR pin signal is outputted LOW during a memory or I/O WRITE. The IO/ $\overline{\rm M}$  signal is outputted high to indicate an I/O operation and is outputted low during a memory operation. The IO/ $\overline{\rm M}$ , S<sub>O</sub>, and S<sub>1</sub> are outputted during its internal operations as shown in Fig. 4.2. (Chapter-IV).

In the present project we have a microcomputer with the 16-bit address bus, 8-bit data bus, and with the necessary control signals (IORD, IOWR). The designed EPROM programmer is interfaced to these buses. The interfacing designs are described in the subsequent Chapters.

#### INTERPACING WITH PERIPHPRAT TWICE

In regard to microcomputer systems, interfacing can be separated into two areas of concern. One area involves the connection of the components, such as memory units and input/output registers, to the buses of a microprocessor. Such interfacing is primarily concerned with the timing and control of the buses and selection of a component so as to effect a data transfer at a given time between the selected component and the microprocessor.

The other area of concern involves interfacing components external to the microcomputer, such as peripheral devices, data channels etc. Such interfacing does not directly involve the buses of the microprocessor; so it is less structured. It is concerned with converting signals associated with the external components, which might be of any nature (including analog), to signals compatible with the buses and vice versa.

An input or output operation is the act of transferring data to or from a selected peripheral device. The microprocessor is the focus of all operation, so an input will mean data flows into the MPU whereas an cutput will mean data flows out of the MPU. Those locations where data is input from or output to are usually called input or output ports.

From the 8085 instruction sets, it appears that it uses the IN and OUT instructions for transferring data to and from I/O ports. These data transfer instructions are illustrated in Fig. 4.1. The output instruction is represented by OUT mnemonic

in assembly language program, while the input instruction uses the IN mnemonic. The instruction formats for these operations are also reproduced in the Fig. 4.1 showing the opcode followed by a device number or port address. The byte long port address can select one of 256 ( $2^8$ ) ports. Mostly the most significant 8 address lines ( $4_8$  -  $4_{15}$ ) are used for the port address.

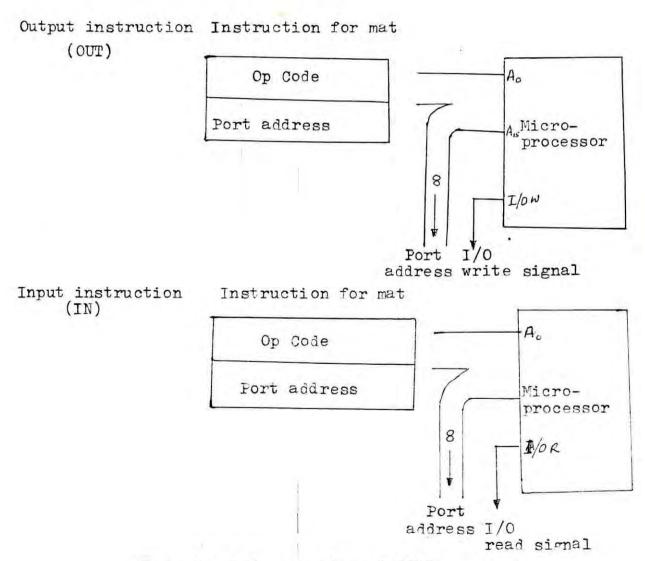


Fig. 4.1 I/O operation of 8085

Fig. 4.1 also shows two additional output control signals added to the microprocessor. When using the OUT operation, a special input/output write  $(\overline{I/OW})$  signal is used. The IN operation also requires the use of a special output signal called input/output read  $(\overline{I/OR})$  signal. Both of these output signals are active LOW signals and are illustrated in Fig. 4.1. The status of the S<sub>o</sub>, S<sub>1</sub> and  $\overline{IO/M}$  pins during various read/write operations are shown in Fig. 4.2.

8085 control signals			Function
IO/M	21	2°	rane of on
0	0	1	Memory write
0	1	0	Memory read
1	0	1	I/O write
1	1	0	I/O read
0	1	1	Op code fetch
1	1	1	Interrupt acknowledge

Fig. 4.2 Control Signal table for I/O.

The data transfer using the IN and OUT instructions are classed as program-controlled I/O. Program instructions are controlling the transfer of data during IN and OUT operations. Program controlled I/O is divided into two techniques:

i. Standared I/O

ii. Memory Mapped I/O

The memory-mapped I/O technique is the most common and can be used with any microprocessor. The standard I/O techniques can be used only with microprocessors that have separate IN and OUT instructions as in the 8085 microprocessor.

It is common to refer to an output as "an output to a peripheral device". In actual practice however, the output from the microprocessor is not directly to a peripheral device but to a memory device which stores the data for the peripheral unit. The intermediate blocks in Fig. 4.3 are the memory devices known as "input interface adapter" or "output interface adapter". It is common for I/O interface adaptor to have characteristics other than memory also.

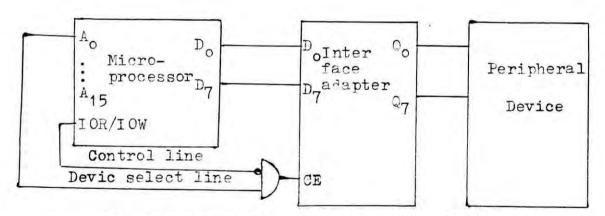


Fig. 4.3 Connection with microprocessor of the peripheral

In the designed EPROM programmer, the peripheral is the EPROM to be programmed housed in the 40-pin socket. The address decoder together with the buffers and latches form the output interface adapter through which address, data and control singual pass to the EPROM. The buffers with the decoder form the 'input interface adapter' through which data to be read or verified is input to the microcomputer (Fig. Chapter-VI).

# CHAPTER - V PROGRAMMING CHARACTERISTICS OF INTEL EPROMS

# 5.1 Comparative Study of the Intel EPROMs

The EPROM Programmer can be used for programming the following type of EPROMs:-

- i. 16k (2k x 8) IV Erasable PROM: Intel 2716
- ii. 32k (4k x 8) UV Erasable PROM: Intel 2732
- iii. 64k (8k x 8) UV Erasable FROM: Intel 2764
  - iv. 128k(16k x 8) UV Erasable PROM: Intel 27128
  - v. 1k x 8 PROM within the Intel 8048H single component 8 bit microcomputer.
- vi. 1k x 8 PROM within the Intel 8748H sin-le-chip microcomputer.

A comparative pin diagram of all the EPROMs is shown in Fig. 5.1. Individual pin diagrams, block diagrams and logic symbols of each of the above EPROMs are given in the appendix.

## 5.2 27-Series EPROM Operation

The EPROMs have the features of fast signle-address location programming and have, an access time from 250 ns to 650 ns and is ideal for use with the high-performance microprocessors. A block diagram is shown in Fig. 5.2 to represent the 27-series EPROMs.

The EPROMs have five modes of operation as listed in Table 5.1 the modes are briefly discussed below which will be helpful in the hardware design.

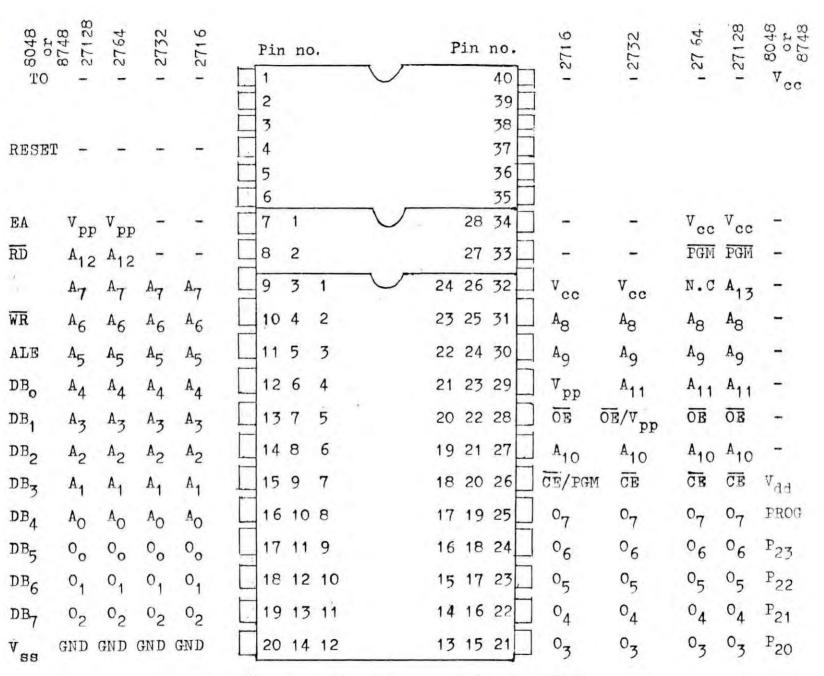


Fig. 5.1 Pin diagram of Intel EPROM

5.2.1 Read Mode: The 27-series EPROMs have two control functions, both of which must be satisfied in order to obtain data at the outputs. Chip Enable  $(\overline{CE})$  is the power control and should be used for device selection. Output Enable  $(\overline{OE})$  is the output control and should be used to gate data to the output pins, independent

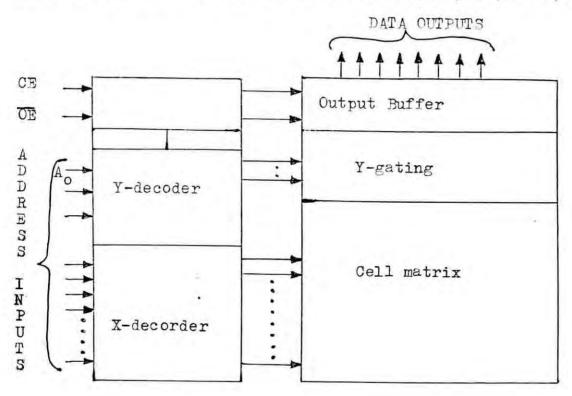


Fig. 5.2 Block diagram of EPROMs.

of device selection.

5.2.2 Standby Mode:- The 27-series are placed in the standby mode by applying a TTL high signal to the  $\overline{\text{CE}}$  input. When in standby mode, the outputs are in a high impedance state, independent of  $\overline{\text{OE}}$  input.

TABLE 5.1 COMPARATIVE STUDY OF MODE SEFECTIONS FOR INTEL EPROMS

(28 pin configuration: EPROMs will be housed in the lower side of socket).

	Pins	CE/PGM (20)	PGM (27)	OE/V	V	Vcc	Vcc	V.nn	Outputs	
Mode	Type of EPROMs	(20)	(27)	OE/V <sub>pp</sub>	(23)	(24)	(28)	V pp (1)	11-13, 15-19	
	2716	VIL	-	VIL	+5	+5	-	-		
READ	2732 2732A	VIL	-	VIL	-	+5	-	<del>-</del>	D	
	2764	AlT	VIH	VII	-	-	+5	+5	Dout	
	27128	VII	VIH	VII	*	o <del>le</del> n	+5	+5		
	2716	AIH	-	X	+5	+5	-	-		
STAND-	2732 2732A	AIH	-	Х	-	+5	-	-	High Z	
BY	2764	ΔlH	X	X	-	-	+5	+5		
	27128	· A <sup>IH</sup>	X	X	-	-	+5	+5		
	2716	Pulsed ${ m V_{IH}}$	L -	V <sub>IH</sub>	+25	+5	-	7 <del>-</del> .		
PRO- GRAM	2732 2732A	VIH	-	25 21	-	+5	-	-	Din	
GILAN	2764	V <sub>IL</sub>	AIT	AlH	-	-	+5	+21	1 111	
	27128	v <sub>II</sub>	VIIx	VIH	\ \ <del>-</del> \		+5	+21		
PRO-	2716	V <sub>IL</sub>	-	VIL	+25	+5	-	-		
GRAM VERIFY	2732 2732A	$v_{\mathrm{IL}}$	-	v <sub>IL</sub>	-	+5	-	-	Dout	
	2764	VIL	VIH	VII	-	-	#5-	+21		
	27128	V <sub>IL</sub>	VIH	VIL	-	-	+5-	+21		
PRO-	2716	VIL	-	VIL	+25	+5	-	-		
GRAM INHIB-	2732 2732A	v <sub>IH</sub>		25 21	-	+5	-	-	Hingh 2	
IT.	2764	V <sub>IH</sub>	X	X	-	-	5	21		
	27128	$v_{IH}$	х	X	-	-	5	21		

### Contd. Table 5.1

- 1. X ---- don't care
- 2. Exceeding 22V on pin 1 ( $V_{pp}$ ) will damage the 2764 and 27128 while programming
- 3. In the program mode the 2732A OE/V<sub>pp</sub> input is pulsed from a TTL low level to 21V (25V for 2732). Exceeding 22V will damaged the 2732A.
- 4.  $V_{cc}$  must remain within 5  $\pm$  5% Volts.
- 5.  $V_{TL} = Input low voltage = 0.1V to 0.8V$
- 6. V<sub>TH</sub> = Input high voltage = 2V to 6V
- 7.  $V_{cc}$  must be applied simultaneously or before  $V_{pp}$  and removed simultaneously or after  $V_{pp}$ .

- 5.2.3 <u>Program Inhibit Mode:- Programming of multiple EPROMS</u> in parallel with different data is also accomplished. Except for  $\overline{\text{CE}}/\text{PGM}$  or  $\overline{\text{CE}}$  or  $\overline{\text{CE}}$  (or PGM)all like inputs (including  $\overline{\text{OE}}$ ) of the parallel 27 -EPROMS may be common. An active signal to the  $\overline{\text{CE}}$  pin of a particular EPROM will program that EPROM and others are inhibited from being programmed.
- 5.2.4 <u>Program Verify Mode:-</u> A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify may be performed with  $V_{pp}$  at 25V (or 21V as the case may be). In case of 2716  $V_{pp}$  should be at 5V except during programming and program verify. In case of 2732, 2764 & 27128 the verify is accomplished with  $\overline{\text{OE}}$  &  $\overline{\text{CE}}$  at  $V_{TL}$  with PGM at  $V_{TH}$ .
- 5.2.5 <u>Programming Mode:-</u> Initially after each erasure, all bits of the EPROMs are in the "1" state. Data is introduced by selectively programming "0's" into the desired bit locations. Although "0's" will be programmed, both "1's" and "0's" may be present in the data word.

# a. Intel 2716 EPROM:

When the address and data are stable, a 50 msec, active-high, TTI program pulse is applied to the OE/PGM input.

### b. The 2732 EFROMs:

The 2732 & 2732A are in the programming mode when  $\overline{\text{OE}}/\text{V}_{\text{pp}}$  = 21V.

When the address and data are stable, a 50 msec, active-low, TTL program pulse is applied to the  $\overline{\text{CE}}$  input. The 2732A must not be programmed with a DC signal applied to the  $\overline{\text{CE}}$  input.

## c. The 2764 & 27128 EFROMs:

The 2764 & 27128 are in the programming mode when  $V_{\rm pp}$  = 21V

 $\overline{\text{CE}} = \overline{\text{PGM}} = V_{T,T}$ 

For programming, CE should be kept TTI low at all times while  $V_{\rm pp}$  is kept at 21V. When address and data are stable, a 50 msec, active low, TTL program pulse is applied to  $\overline{\rm PGM}$  input.

For all the above EPROMs the data to be programmed is applied 8 bits in parallel to the data output pins. The levels required for the address and data inputs are all TTL. A program pulse must be applied at each address location to be programmed. Any location can be programmed at any time-either individually, sequentially or at random. The program pulse has a maximum width of 55 msec<sup>5</sup>.

# 5.3 Programming of 8748H & 8048H EPROM

The programming process consists of:

- i. activating the program mode
- ii. applying an address
- iii. latching the address
  - iv. applying data
    - v. applying program pulse.

Each word is programmed completely before moving on to the next and is followed by a verification step. The following is a list of the pins used for programming and a description of their functions:

Pins	Function
XTAL 1	Clock input 1 to 3 MHz
Reset	Initialization and address latching
Test O	Selection of program or Verify mode
EA	Activation of Program/Verify mode
BUS	Address and data input, data output during verify
P <sub>20</sub> -P <sub>22</sub>	Address input
$v_{ m DD}$	Programming power supply
PROG	Program pulse input

The program/verify sequence is:

- 1.  $V_{DD} = 5V$ , clock applied or internal oscillator operating  $R_{\text{p}} \overline{\text{Set}} = 0V$ , TEST 0 = 5V, EA = 5V, BUS and PROG floating,  $P_{10}$  and  $P_{11}$  must be tied to ground.
- 2. Insert 8748H in programming socket.
- 3. TEST 0= OV (select program mode).
- 4. EA = 18V (activate program mode)
- 5. Address applied to BUS and  $P_{20}$   $P_{22}$ .
- 6. RESET = 5V (latch address)
- 7. Data applied to BUS

- 8. V<sub>DD</sub> = 21V (programming power)
- 9. PROG = OV followed by one 50 msec pulse to 18V
- 10.  $V_{DD} = 5V$
- 11. TEST 0 = 5V (verify mode)
- 12. Read and verify data on BUS
- 13. TEST 0 = 0V
- 14. RESET= OV and repeat from step 5
- 15. Programmer should be at conditions of step 1 when the EPROMs are removed from socket.

### CHAPTER - VI

### HARDWARE DESIGN OF EPROM PROGRAMMER

### 6.1 Functional description of EPROM Programmer

A simplified block diagram of the EPROM porgrammer is shown in Fig. 6.1 and consists of the following major blocks.

- a. The address decoder (ADDEC)
- b. The I/O data buffers (DABUF)
- c. The expansion buffer (EXBUF)
- d. The address latches
  - i. Lower address latch (ADL)
  - ii. Higher address latch (ADH)
- e. The data latch
  - i. EPROM data latch (DR)
  - ii. Frinter data latch (PRT)
- f. The control latches
  - i. Port controlling latch (PCR)
  - ii. EPROM controlling latch (CR)

The address decoder is used to select the address, data and control latches and the I/O buffers and the expansion buffer. The B8 to BF (Hexadecimal) address range is used by the address decoder for the selection purpose.

The I/O data Buffers are used for transferring data to and from the microcomputer. The expansion buffer is reserved for future expansion of the system.

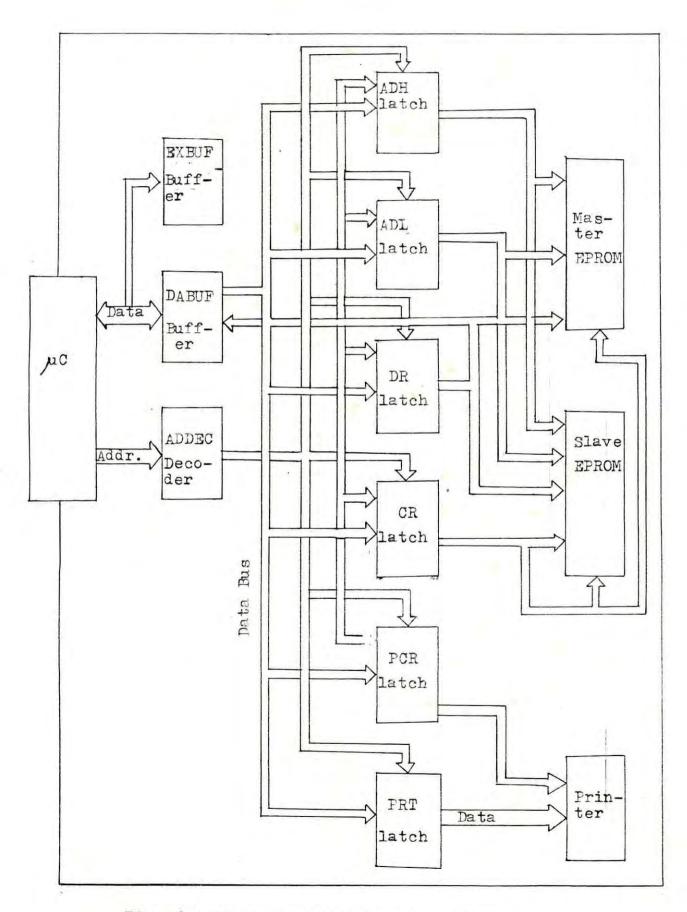
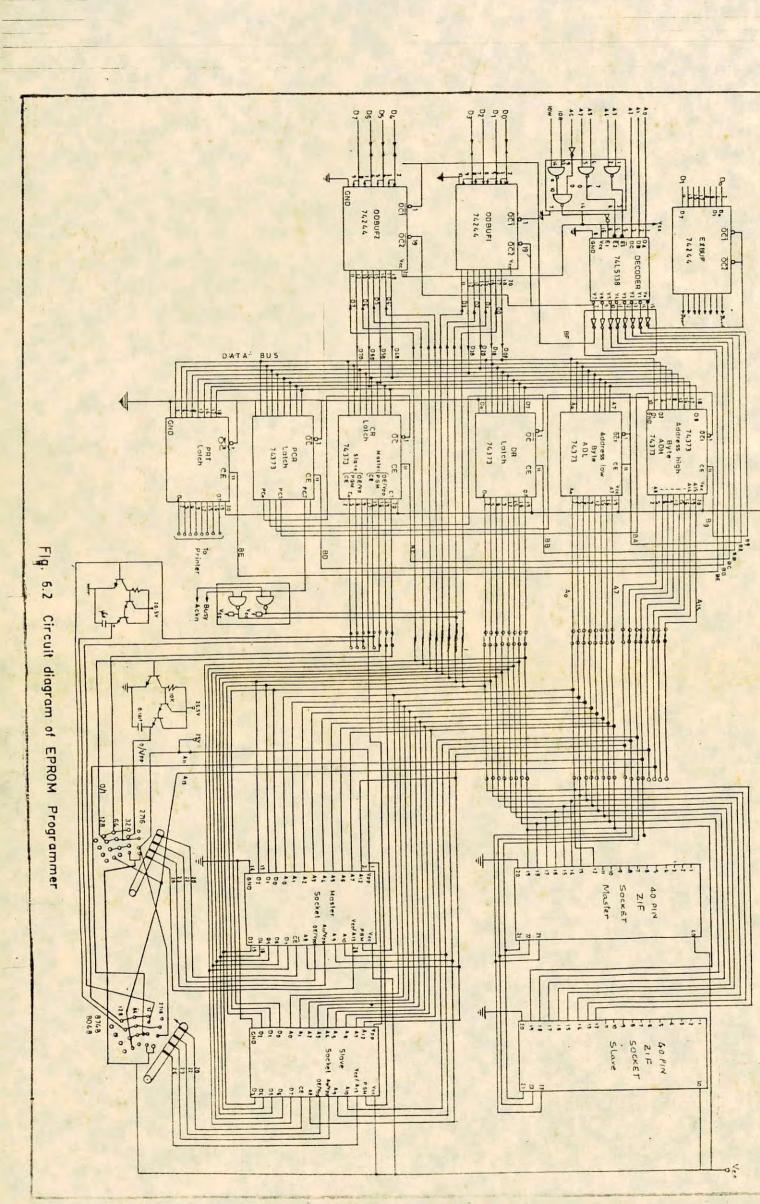


Fig. 6.1 Block Diagram of EPROM Programmer



The control latches are used for sending various signals to the EPROMs for the mode selections and also for controlling the remaining latches. Control lines are program-controlled so that the Intel EPROM series (2716, 2732,2764, 27128 etc.) can be programmed.

The data latches are used to latch the data to be programmed and upon receiving output control  $(\overline{OC})$  signal they send the data to the desired location.

The address latches are used to latch the address of the location of the EPROM to be programmed and upon receiving the output control signal they put the address on the desired pins of the EPROM.

# 6.2 Detail Circuit Diagram of the EPROM Programmer

A detailed schematic diagram of the designed EPROM programmer is shown in Fig. 6.2. The description of each functional unit is given below.

# 6.2.1 The address decoder (ADDEC)

There are six latches and two sets of buffers in the designed programmer. Their address are to be B8 to BF. This is accomplished with the help of the 3-line to 8-line decoder (74LS138) IC Chip in conjunction with the 2-imput NAND gates. The pins  $D_A$ ,  $D_B$ ,  $D_C$  of the decoder are connected to the  $A_8$ ,  $A_9$  and  $A_{10}$  lines respectively of the address bus of the microcomputer.

The six outputs  $(\overline{Y}_1 \text{ to } \overline{Y}_6)$  bearing the address B9 to BE, of the decoder are connected to the chip Enable (CE) pin of the six latches, after being inverted by the 7404 inverter, as because the Chip Enable of the latches are active High. The addresses of all the latches and buffers are given in Table 6.1.

Table 6.1 Address of the Latches

Sl.No.	Name of the latch/Buffer	Address designated (in hexadecimal)	CE/OC(Buffer connec- tion with decoder pin	
1.	I/O Data Buffer(DABUF1 & DABUF <b>2)</b>	B8	Y <sub>0</sub> (Pin 15)	
2.	Higher address latch(ADH)	В9	Y <sub>1</sub> (Pin 14)	
3.	Lower address latch(ADL)	BA	Y <sub>2</sub> (Pin 13)	
4.	EPROM Data latch(DR)	BB	Y <sub>3</sub> (Pin 12)	
5.	EPROM controlling latch (CR)	BC	Y <sub>4</sub> (Pin 11)	
6.	Port control latch(PCR)	BD	Y <sub>5</sub> (Pin 10)	
7.	Printer data latch(PRT)	BE	Y <sub>6</sub> (Pin 9)	
8.	Expansion Buffer(EXBUF)	BF		

If the CE pin of a particular latch is HIGH, the contents of the data bus will be latched in the register. The CE pin will be HIGH when the specified latch is addressed. This data will be outputted only when the output control  $(\overline{OC})$  pin is LOW. This  $\overline{OC}$  pin is controlled by the port control register (PCR).

Using this decoder the following binary format of the high address bus (Fig. 6.3) may be used for address selection between B8 to BF.

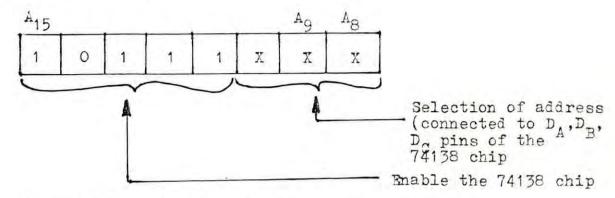


Fig. 6.3 Addressing format of the address decoder.

The decoder should be enabled with the above address only during input/output operation i.e., when  $\overline{\text{IOR}} = 0$  or  $\overline{\text{IOW}} = 0$ .

The decoder for decoding the address has three enabling pins,  $\overline{\mathbb{E}}_3$ ,  $\overline{\mathbb{E}}_2$ , which are active low and  $\mathbb{E}_1$  which is active high. The decoder will output LOW at one of its 8 output pins depending on the value of  $\mathbb{D}_A$ ,  $\mathbb{D}_B$ ,  $\mathbb{D}_C$  inputs when all three pins  $\overline{\mathbb{E}}_3$ ,  $\overline{\mathbb{E}}_2$  and  $\mathbb{E}_1$  are activated.

The input to  $\overline{E}_3$  pin is from the output pin of a NAND gate whose inputs are  $A_{11}$  and  $A_{12}$  lines of the address bus and that to  $\overline{E}_2$  pin is from the output of another NAND gate whose inputs are  $A_{13}$  and  $A_{15}$  lines of the address bus. So  $\overline{E}_3$  and  $\overline{E}_2$  are selected only when  $A_{11} = 1$ ,  $A_{12} = 1$ ,  $A_{13} = 1$  and  $A_{15} = 1$ . Another logic circuit is necessary to select  $E_1$  such that  $E_1$  will be high only when  $A_6 = 0$  and IOR = 0/IOW = 0. Accordingly the input to  $E_1$  pin will come from a logic circuit which will follow the

its truth table and Karnangh map involving the don't care conditions as given in Fig. 6.4

IOW	IOR	A <sub>14</sub>	Output E1
0	0	0	đ
0	0	1	đ
0 .	1	0	1
0	1	1	0
1	0	0	1
1	0	1	0
1	1	0	0
1	1	1	0

	TOILLOW	TORION	TORIOW	TORIOW
Ā <sub>14</sub>	d	1		1
A <sub>14</sub>	đ			
	-			

TORTOW TORTOW TORTOW TORTOW

Fig. 6.4(a) Truth table.

Fog. 6.4(b) Karnaugh map

The boolean function of the above truth table will be

$$E_{1} = \overline{A_{14}} \overline{10W} + \overline{A_{14}} \overline{10R}$$

$$= \overline{A_{14}} + \overline{10W} + \overline{10R}$$

$$= \overline{A_{14}} + \overline{10W} \cdot \overline{10R}$$
Fig. 6.5 Logic Circuit for the above truth table

Therefore the logic circuit becomes as shown in Fig. 6.5.

A<sub>14</sub>· IOW.IOR

# 6.2.2 I/O and Expansion Buffers (DABUF1, DABUF2, EXBUF)

74LS244 buffers are used which has two control pins. Each control pin controls four bits of data. The  $\overline{\text{OC}1}$  controls four output bits and  $\overline{\text{OC}2}$  controls four input bits. Two buffers are used for handling eight outgoing and eight incoming bits. The two buffers DABUF1 and DABUF2 are used for transferring data to microcomputer received from the EPROM in case of reading and verifying the EPROM content and for receiving data from the microcomputer for onward transmission to different latches via the data bus. The address of these two bus buffers are B8. These buffers are designed to be always in the output mode by connecting the  $\overline{Y}_0$  output of the decoder after being inverted by the inverter to  $\overline{\text{OC}1}$  pins of the buffers. The output control pins  $\overline{\text{OC}1}$  and  $\overline{\text{OC}2}$  are active LOW.

For all OUT instructions (OUT B9 to OUT BF), the decoder ontput pin  $\overline{Y}_0$  (pin 15 of 74138) will be HIGH and after being inverted it will be LOW. Therefore these buffers will be always in the output mode and data will be outputted to the data bus from the microcomputer. The output pin  $\overline{Y}_0$  is directly connected to the output control  $\overline{OC2}$  pin of the buffers. So that when IN instruction to address B8 is executed only then the pin  $\overline{Y}_0$  is LOW and these buffers are in the input mode as  $\overline{OC2}$  is directly connected to  $\overline{Y}_0$  of decoder and data from the specified address of the EPROM will be inputted to the buffers and will be transmitted to the microprocessor. The output pin  $\overline{Y}_7$  is directly connected to the expansion buffer (EXBUF) and here 8-bit data can only be

outputted and cannot be inputted.

### 6.2.3 The Address High and Address Low Registers (ADL & ADH)

The address high latch (ADH) is used for latching the high byte address ( $A_8$ - $A_{15}$ ) and the latch ADL is used for latching low byte address ( $A_0$ - $A_7$ ) of the EPROM to be programmed. At first the high byte address of the location of the EPROM is loaded in the accumulator of the microprocessor. Then the content of the accumulator is transferred to the ADH latch using the instruction OUT B9. When OUT B9 instruction is used the  $\overline{\text{OC}1}$  pins of the two data buffers (DABUF1, DABUF2) LOW and the CE pin of the latch ADH is high and hence the content of the accumulator is transferred to the ADH latch and is latched there. In the same manner the LOW byte address of the location of the EPROM is latched in the ADL latch. Here the instruction transferring the low byte address is OUT BA. The  $\overline{\text{OC}}$  pin remains high so that output is 3-stated. The  $\overline{\text{OC}}$  pins of all the latches is controlled by the port control register (PCH) latch.

# 6.2.4 The Data latches (DR & PRT Latches)

The data to be transferred to the location specified by the content of the ADH and ADL latches is loaded in the accumulator and is transferred and latched in the Data register (DR)using the instruction OUT BB. Its output control  $(\overline{OC})$  pin also remains high. The output control  $\overline{OC}$  is activated by the second bit of the PCR latch.

In a similar way data is transferred to the latch PRT using the instruction OUT BE. It's  $\overline{OC}$  pin is grounded so that it is

of the latch PCR.

Port control latch (PCR) controls the output pin  $(\overline{OC})$  of the remaining latches. Control information is transferred to the PCR from accumulator using the instruction OUT BD. Output control pin  $(\overline{OC})$  is grounded so that whenever its chip enable (CE) pin is high, the content of the data bus is latched in the PCR and is outputted at the same time. The format of the Port control latch for output selection of the remaining latches are shown in Fig. 6.6.

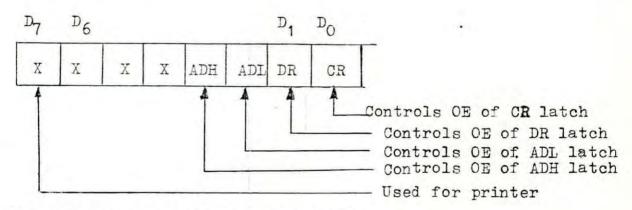


Fig. 6.6 Format of Port control latch

When the output Q is Low, the corresponding latch outputs the latched data in it.

Table 6.2 Control Commands for Various Functions on the EPROMs

	Type of	Control Signal								
Mode	EPROM	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3		Bit 1	Bit O	Hex
READ MASTER	2716 & 2732	1	X	1	0	Х	0	Х	X	
	2764 & 27128	1	X	1	0	1	0	X	X	
READ SLAVE	2716 & 2732	0	X	0	1	X	1	Х	X	
	2764 & 27128	0	1	0	1	X	1	X	X	
PROGRAM MASTER	2716	1	X	1	1		Pulsed V <sub>IL</sub> to VIH	X	X	
	2732	1	X	1	0	X	1	X	X	
	2764 128	1	1	1	1	0	0	X	X	
PROGRAM SLAVE	2716	1	X F V	ulsed IL to	1	X	, 1	X	Х	
	2732	1	X	1	1.	1	1	X	X	
	<b>2</b> 764 128	1	0	0	1	1	1	X	X	
PROGRAM. V <b>B</b> RIFY	2716	1	X	1	0	X	0	X	X	
	2732	1	X	1	0	X	0	X	X	
	2764 128	1	X	1	0	1	0	X	Х	
PROGRAM	2716	0	X	0	1	X	1	X	X	
VERIFY SLAVE	2732	0	X	0	1	X	1	X	X	
mav n	2764 128	0	1	0	1	X	1	X	X	

# 6.3 Connection of the EPROM Pins

From a comparative study of the pin diagrams of all the EPROMS (Fig. 5.4) it can be seen that the 27-series EPROMS pin diagrams are almost similar. The difference in the pin connections are shown in Table 6.3. A MASTER IC socket (40 pin) and a SLAVE IC socket (40 pin) with zero insertion force (ZIF) are used for placing any of the EPROMS type during programming. The EPROMS are always placed at the bottom of the socket as shown in Fig. 5.1. Since the 8048H and 8748H microcomputer EPROMS differ significantly from the 27-series, a different connecter is used for programming but with the same ZIF socket. The two connecter connection can be seen from the detailed circuit diagram in Fig. 6.2.

The address pins  $A_0$ - $A_7$  are connected to the 8 output pins  $D_0$ - $D_7$  of the ADL latch. The next three address pins  $A_8$ - $A_{10}$  and  $A_{12}$  are also connected permanently to the three lower output pins  $D_0$ - $D_2$  and  $D_4$  lines of the ADH latch. The  $A_{11}$  and  $A_{13}$  pins are connected to the  $D_3$  and  $D_5$  pins of the ADH latch via the selector switch because the connection of these pins are variable for diff. EPROMs.

The data pins  $D_0-D_7$  of EPROMs are connected to the output pins  $D_0-D_7$  of DR latch and also they are connected directly to the eight input pins of the buffers DABUFI & DABIUF2 so that the data can be inputted to the  $\mu$ C directly when needed. The data of either slave of Master EPROM will be inputted to the

Table 6.3 Difference in the Pin connections of different EPROM

Pin No. 28-Pin Confi- guration	Pin no. 24-Pin configu- ration	2716	2732	2764	27128	Comment
1	-	-	1000	v <sub>pp</sub>	V <sub>pp</sub> }	May be connected permanently to
2	-		<del>-</del>	A12	A <sub>12</sub>	socket
3-19	1 - 17	$(A_0 - A_7)$ and	$(0_0 - 0_2)$ and	GND and (03	- 0 <sub>5</sub> )	Same for all EPROMs
20	18	CE/PGM	CE	CE	CE }	
22	20	OE	OE/V <sub>pp</sub>	OE	OE {	Variable on type
23	21	V <sub>pp</sub>	A <sub>11</sub>	A <sub>1 1</sub>	A 1 1	of EPROM So a switch is to
26	24	Vcc	V <sub>ee</sub>	n.c	A <sub>13</sub>	be used
27	1.4.	-	-	PGM	PGM )	May be connected
28	-	4	-	v <sub>cc</sub>	v <sub>cc</sub>	permanently to socket.

microcomputer via the buffers depending on whose  $\overline{\texttt{OE}}$  enable is activated. The programming voltage is supplied to the programming pins in case of programming an EFROM at either Master or Slave location from an outside source of 25V or 21V as the case may be. Since the +25V V<sub>pp</sub> required by the EPROM must be off except when programming or verifying, the switch is designed to be in the off state when the processor is turned on. A high on the switch input turns it off.

With the switch off, the diode to +5V turns on and supplies the  $V_{\rm pp}$  (for 2716) pin with the voltage required for normal read operation. This input is controlled by the CR register output. When the switch to 25V is on, the diode is reverse biased. The switching circuit is shown in Fig. 6.7.

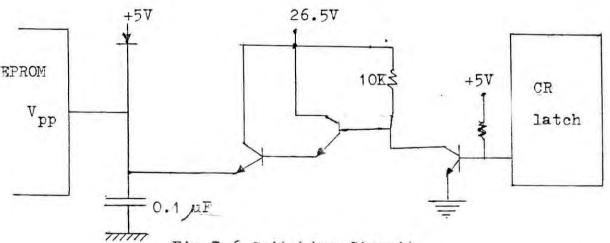


Fig. 7.6 Switching Circuit

Due to voltage drop across transistor a higher voltage than 25V(or 21V) must be used as the switch supply. A 0.1  $\mu\text{F}$  capacitor on the  $V_{\text{pp}}$  pin helps prevent overshoot which might destory the EPROM during switching.

### CHAPTER - VII

### SOFTWARE DEVELOPMENT

### 7.1 Functions of the Programmer

The following operation will be performed by the microprocessor-based programmer.

- 1. Loading the data to be programmed from a selected input device (Tape, EPROM etc.) into the micro-computer memory.
- 2. Programming a segment of a PROM with the data which are stored begining at a specified address in the microcomputer memory.
- 3. Displaying the contents of a segment of a PROM at the Master or Slave location or of the main memory on the monitor screen.
- 4. Moving a block of data from one memory location to another memory location.
- 5. Transferring a block of data in a PROM into the microcomputer memory so that the contents of the PROM may be verified or examined through the system and may also be used to duplicate a PROM.
- 6. Transferring a block of data from a PROM to the printer to make a hardcopy of the content.

- 7. Comparing a block of data in a PROM with the contents of a segment of memory (Program Verification).
- 8. Verifying a segment of a PROM to see whether the segment is erased.
  - 9. Printing the contents of a segment of memory.

Hardware has been designed so that data to be programmed into the EPROM can come from another ROM/EPROM or from RAM via CPU.

# 7.2 Program Development for the Programmer

Flow diagram of the program to perform the functions described above is shown in Fig. 7.1. To perform the operations as shown in the flow diagram seven subprograms are used. These subprograms are called by the main program (Main Menu) as desired by the user. The names and functions of subprograms are as follows:

- i. READ: Used to read the contents of an EPROM at Master location or at slave location and store it to a desired memory location.
- ii. MOVE: Used for moving a block of data from a certain memory location to another location.
- iii. DISPLAY: Used to display the contents of an EPROM at Master location or at Slave location.

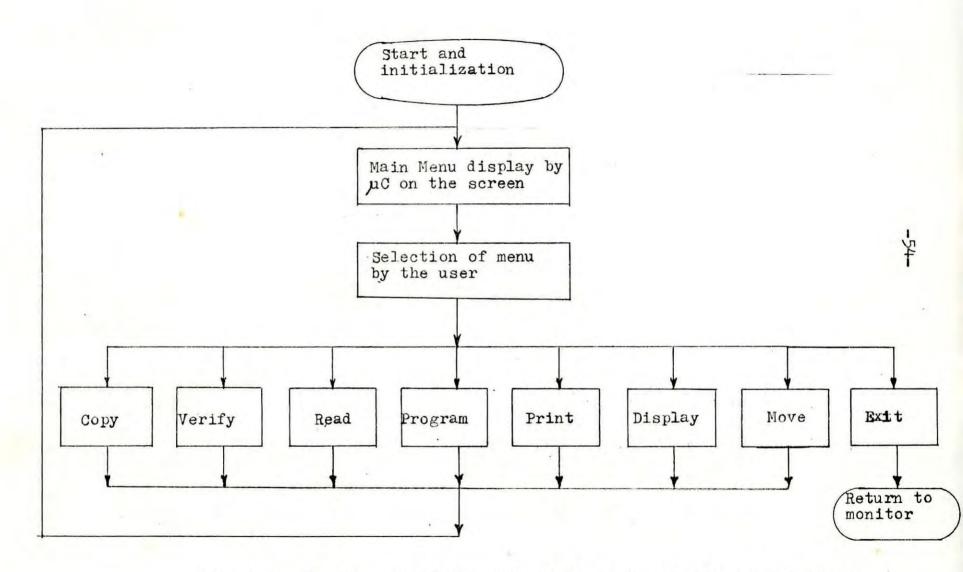


Fig. 7.1 Flow diagram of the program to perform different functions.

- iv. VERIFY: Used to verify if any desired segment of the EPROM at Slave or at Master location erased.
- v. COPY: Used for copying an EPROM in Slave location from an EPROM at Master location.
- vi. PROGRAM: Used for programming any segment of the EPROM at Master location from the main memory.
- vii. PRINT: Used for printing the data from the main memory or from EPROM at Master or Slave location.

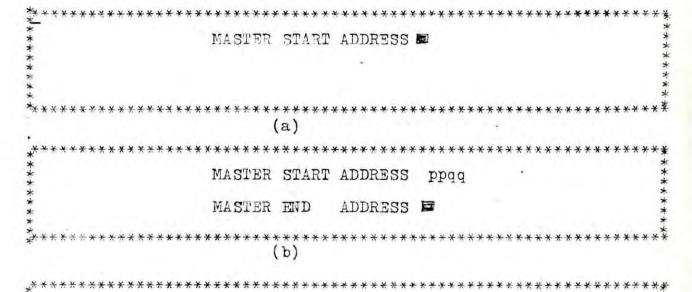
The different variable names used in these subprograms are given in Table 7.1.

When the program is executed main Menu will be shown on the monitor screen of the system. The format of the main Menu as will be shown on the screen is shown in Fig.7.2. There are seven choices of operations to be performed as shown in the figure and for each choice there is a corresponding key to be pressed on the key board. After pressing a particular key the corresponding operation format for the corresponding function will be displayed on the screen. Now the different operations will be discussed in the following sections.

# 7.2.1 READ Subprogram

Read subprogram is used to read the contents of an EPROM at Slave or Master location and store it to a desired memory location. After the main Menu is displayed if the

Once the source EPRCM is selected, the microcomputer waits for the start and end address of the EPROM and also for the destination address in the memory of the microcomputer starting from which data block from the EPROM will be stored. Each of the address will be entered by the user from the key board interactively The interaction of the user and the computer for transferring data from the Master EPROM is shown in Fig. 7.4(a), (b), (c). As each line of the prompt is displayed the corresponding address is to be entered with carriage return at the end. Next line appears only after the previous line is entered. The typed address can be corrected using the cursor movement.



MASTER START ADDRESS ppqq
MASTER END ADDRESS mmnn
TO MEMORY START ADDRESS

(c)

Fig. 7.4 Interactive displays of Master EPROM for READ operation.

An overall flow chart of the Read program is shown in Fig. 7.5(a).

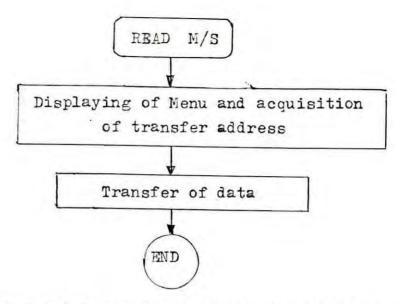


Fig. 7.5 (a) Overall Flow Chart for READ Program

The detailed flow chart of read display menu. is shown in Fig. 7.5(b) and that of the actual data reading is given in Fig. 7.5(c). The detail program is given in the appendix.

# 7.2.2 Conversion of an ASCII-coded hexadecimal number to its binary equivalent

Data to be read from Master from a certain address, to be programmed in Slave from certain address etc. are entered by punching the number on the key board manually. This number is to be stored in the specified address. A chart for the specified address and thier functions are given in the Table 7.2.

When a key containing a number is pressed its ASCII code is loaded in the accumulator. This ASCII code should be converted

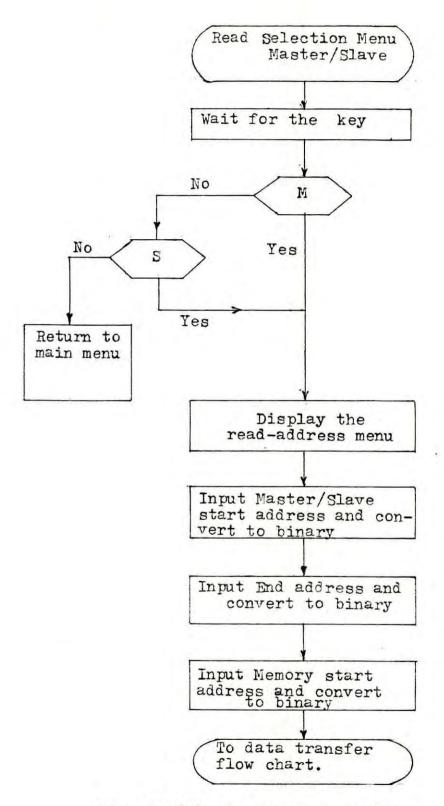


Fig. 7.5(b) Display of Read Menu and acquisition of address flow chart.

READ an EFROM at Master/Slave location

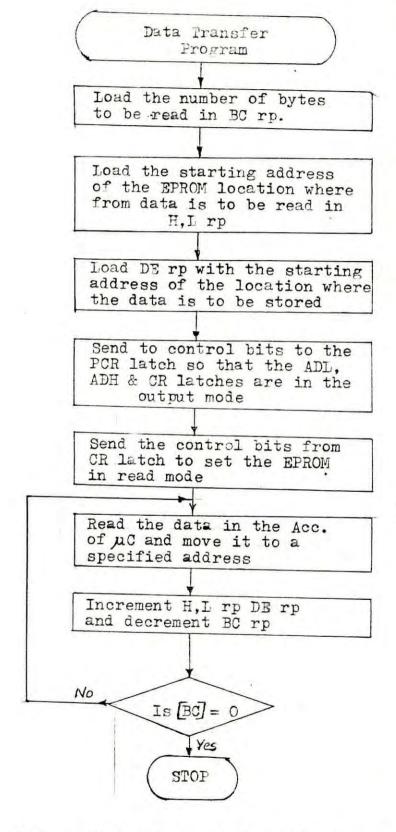


Fig. 7.5(c) Flow chart for Data Transfer for READ operation.

to the corresponding number and then stored in the specified memory location. One byte should be stored in one memory location.

It can be seen from the Table that ASCII Code for the number 0 through 9 are 30 Hex to 39 Hex and A through F are 41 Hex through 46 Hex. So to convert 30H through 39H to number 0 through 9, 30H is to be subtracted or four high bits are to be cleared, and to make 41H to 46H to Hex number A through F, 37<sub>16</sub> is to be subtracted.

The flow chart for ASCII-code to binary conversion routine required for each entry of the address is shown in Fig. 7.6.

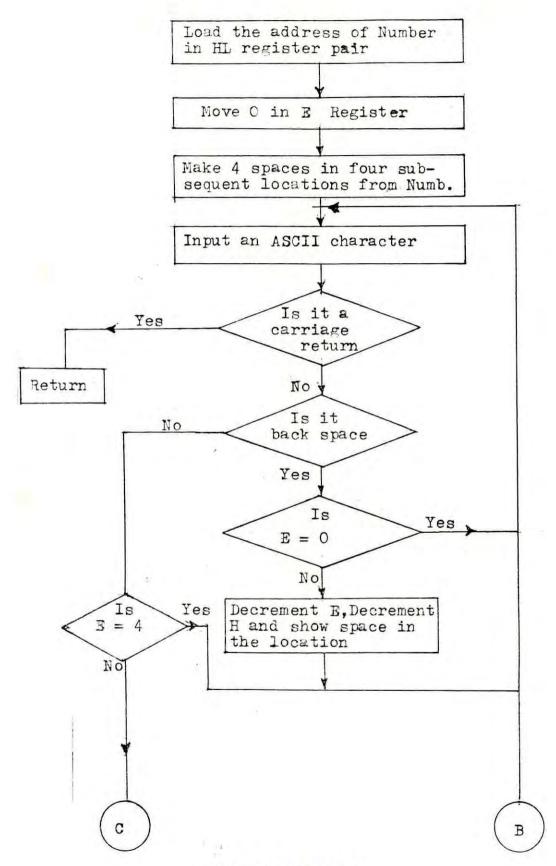


Fig.7.6 (Contd.)

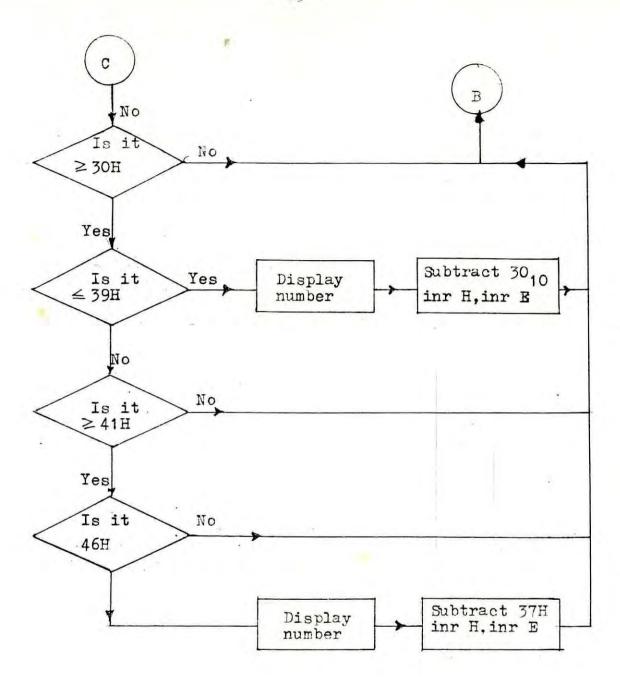


Fig. 7.6 Flow chart for ASCII to binary conversion

### 7.2.3 MOVE Subprogram

It is used for transferring a block of data from a certain memory location to another memory location. After the main Menu is displayed on the screen, if the key M is pressed, the screen will display the MOVE Menu as shown in Fig. 7.7(a)

### M : MOVE DATA FROM MEMORY TO MEMORY

MEMORY START ADDRESS

Fig. 7.7(a)

The cursor will be at the position shown. The starting address will have to be entered manually. After entering the address if carriage return key is pressed the format shown in Fig. 7.7(b) will be displayed with the cursor shown at the position. Ending address will have to be entered manually.

# M : MOVE DATA FROM MEMORY TO MEMORY

MEMORY START ADDRESS ppgg

UNTIL E

Fig. 7.7(b) Interactive Displays of Move Menu

\*\*\*\*\*\*\*\*\*\*\*\*\*\*\*

The CR key will have to be pressed to get the next instruction and the farmat shown in Fig. 7.7(c) will be displayed. The memory starting address wherefrom the data is to be stored will have to be entered manually.

M : MOVE DATA FROM MEMORY TO MEMORY

MEMORY START ADDRESS ppag

\*<del>\*</del>

\*\*\*\*\*\*\*\*\*\*\*

UNTIL mmnn

TO MEMORY START ADDRESS

Fig. 7.7(c) Interactive Displays of Move Menu

The flow chart consists of mainly two parts:

- i. Dispalying of the operating format and entering the starting and ending addresses.
- ii. Transferring the data from one location to another location.

The flow charts are shown in Fig. 7.8(a) and 7.8(b).

# 7.2.4 DISPLAY Subprogram

It is used to display the contents of an EPROM at Master location or at Slave location. In this operation the data is to be fetched from the EPROM at Master or slave location and is to be displayed on the screen instead of storing in the memory with the difference that in DISPLAY routine the contents are displayed instead of being stored and in READ operation the data are stored in memory.

The operation and flow chart are similar to the READ subprogram excepting that instead of moving the fetched data to the memory location it is displayed.

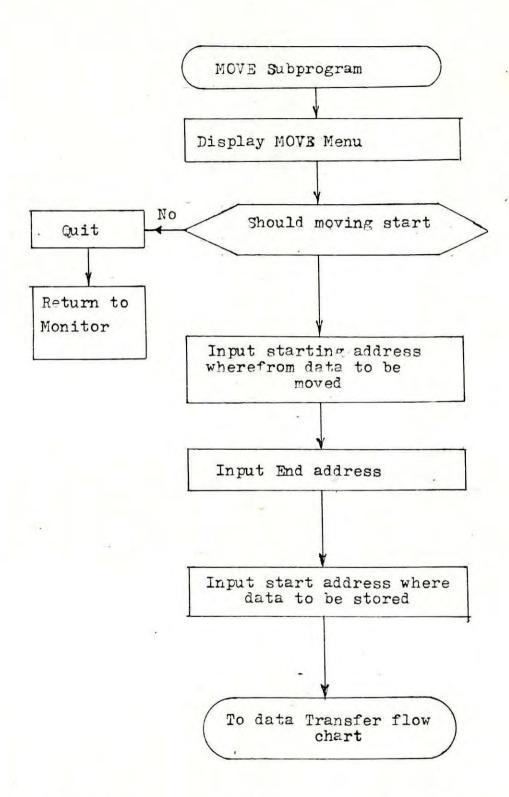


Fig. 7.8(a) Flow chart for MOVE Menu display and address entry.

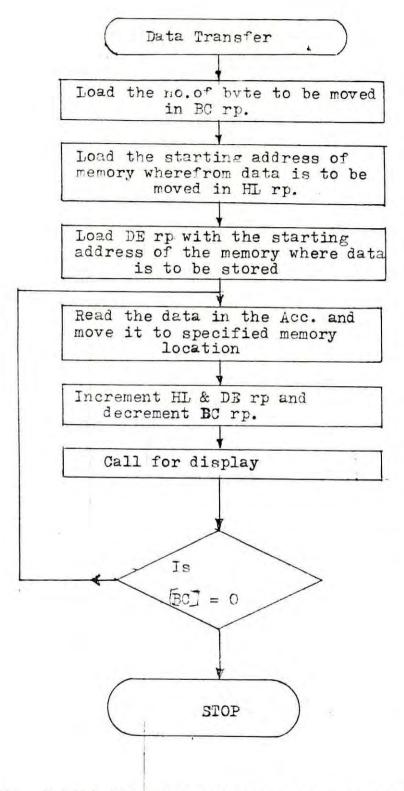


Fig. 7.8(b) Flow Chart for Transfer of Data from Memory to Memory.

#### 7.2.5 VERIFY Subprogram

\*\*\*\*\*\*\*

It is used to verify whether any segment of an EPROM at Master or Slave location is erased. Here data is to be fetched from the EPROM and read and displayed on the screen to see whether EPROM is erased. After the main menu (Selection menu) is displayed on the screen, if the key V is pressed, verify Menu will be displayed as shown in Fig. 7.9(a).

\*\*\*\*\*\*\*\*\*

V. VERIFY MASTER/SLAVE EPROM ERASED

SELECT EPROM

MASTER [M]

SLAVE S

After the verify menu is displayed, if M is pressed the EPROM at Master location will be verified and if S is pressed the EPROM at slave location will be verified.

As in the case of READ, once the source EPROM is selected the microcomputer waits for the start and end address of the block of EPROM to be verified.

The figures that will be displayed after pressing the M key is shown in Fig. 7.10(a) and (b). Each of the addresses will have to be entered by the user from the key board interactively. Only four figures can be entered and may be corrected by shifting the cursor. Next line will be displayed only after the previous

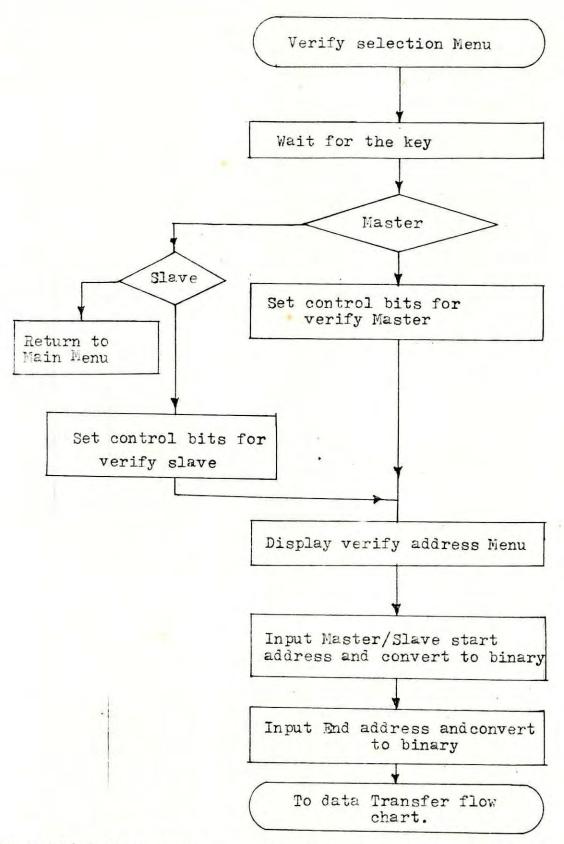


Fig. 7.11(a) Flow chart for displaying menu and acquisition of addresses for VERIFY.

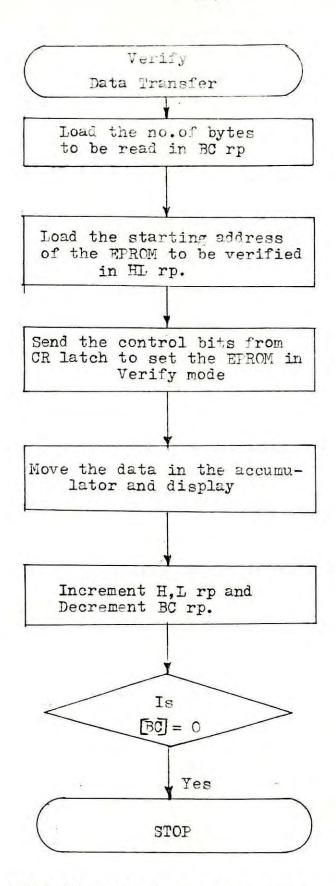


Fig. 7.11(b) Flow Chart for Transferring data for VERIFY.

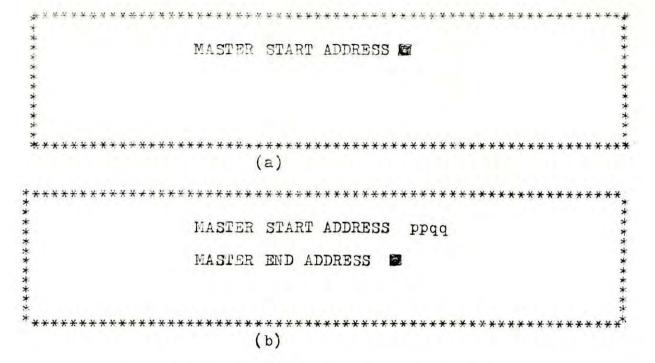


Fig. 7.10 Interactive Displays of Verify Menu

line is entered with carriage return at the end.

The detailed flow chart for displaying and address entering is shown in Fig. 7.11(a) and that of data transfer is shown in Fig. 7.11(b).

#### 7.2.6 PROGRAM Subprogram

This program is used for programming any segment of the EPROM at Master location from the data stored at a certain memory location. After the main menu is displayed if key P is pressed, program menu as shown in Fig.7.12(a),(b) and (c) will be displayed on the screen one after the other.

# P: FROGRAM MASTER EPROM FROM NEMORY MEMORY START ADDRESS

(a)

#### P: PROGRAM MASTER EPROM FROM MEMORY

MEMORY START ADDRESS ppqq
MEMORY END ADDRESS

(b)

P: PROGRAM MASTER EPROM FROM MEMORY
MEMORY START ADDRESS ppqq

MEMORY END ADDRESS mmnn

EPROM START ADDRESS

(c)

Fig. 7.12 Interactive Displays of Program Menu

As in the previous cases, here also the start address will have to be entered manually and only after the start address has been entered with carriage return at the end, the next line will appear with the cursor at the position shown. The typed data can be corrected by moving the cursor.

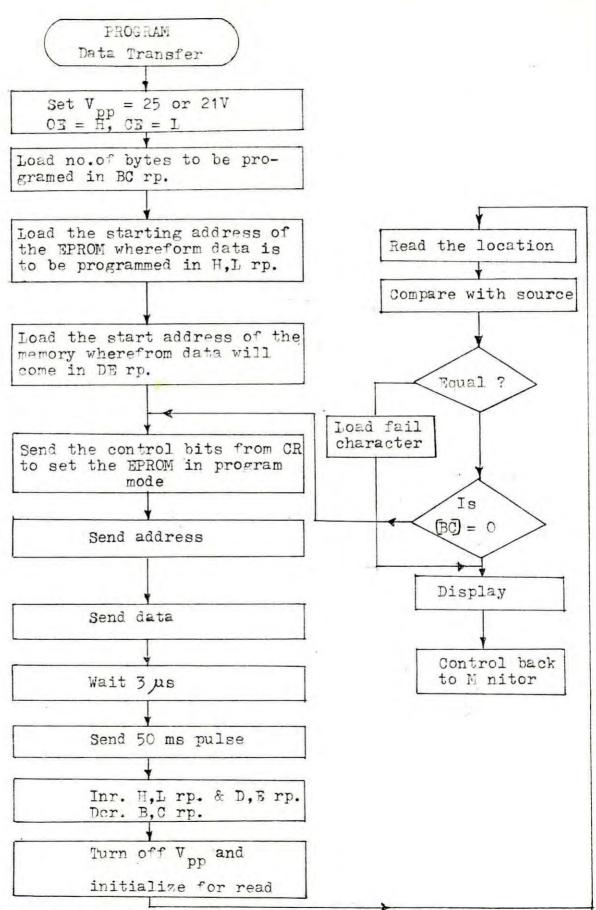


Fig. 13(b) Flow chart for transfer of data for program operation.

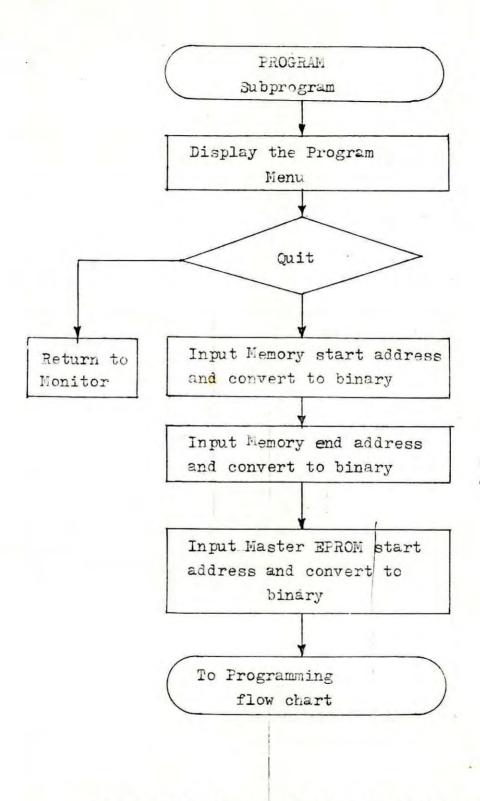


Fig. 7.13(a) Flow Chart for Display of Program Menu and Acquisition Start and End Address.

As in the other cases, here also the flow chart can be divided in two sections, (i) Displaying the Program Menu and entering the start and end addresses of the memory where the data to be programmed is stored and the start address of the EPROM wherefrom programming is to begin and (ii) programming the EPROM.

The detailed flow charts are shown in Fig.7.13(a) and(b). Programming waveforms and programming characteristics of Intel MPROM are given in APPENDIX-B. To program the device, V<sub>pp</sub> is first raised to 25V or 21V as the case may be. The desired address is applied to the device, and  $\overline{\text{OE}}$  is raised to a high state. The data byte is then applied to the device. At least 2 as after the data is stable, a 50 ms program pulse is applied. Data must be held low for at least 2 as after the program pulse goes low. After a location is programmed,  $\overline{\text{OE}}$  can be taken low and location read to see if the programming was successful. It  $\overline{\text{OE}}$  is left high, the data and address for the next location can be sent and then another 50 ms programming pulse applied to the  $\overline{\text{CE}}/\text{PGM}$  pin. The address will be incremented after each location is programmed.

### 7.2.7 COPY Subprogram

COPY subprogram is used to copy a block of data/an EPROM in Master location into an EPROM at Slave location. Data is first fetched from the EPROM in Master location by activating

its output enable pin and then sending the data to the EPRCM at Slave location in programming mode and then verifying whether the EPROM at slave location is correctly programmed. After the main menu is displayed if key C is pressed, Copy Menu as shown in Fig.7.15(a),(b) and (c) will be displayed on the screen one after another.

\*\*\*\*\*\*\*\*\*

\*\*\*\*\*\*\*\*

# C: COPY INTO SLAVE FROM MASTER

MASTER START ADDRESS

(a)

#### C: COPY INTO SLAVE FROM MASTER

MASTER START ADDRESS PPqq
MASTER END ADDRESS

(b)

#### C: COPY INTO SLAVE FROM MASTER

MASTER START ADDRESS ppqq
MASTER END ADDRESS mmnn
SLAVE START ADDRESS

(c)

Fig. 7.15 Interactive Display of COPY Menu.

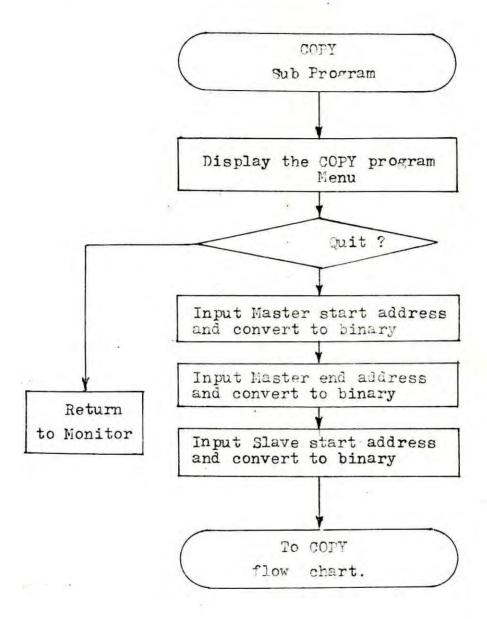


Fig. 7.16 (a) Flow chart for displaying and acquisition of address in COPY mode.

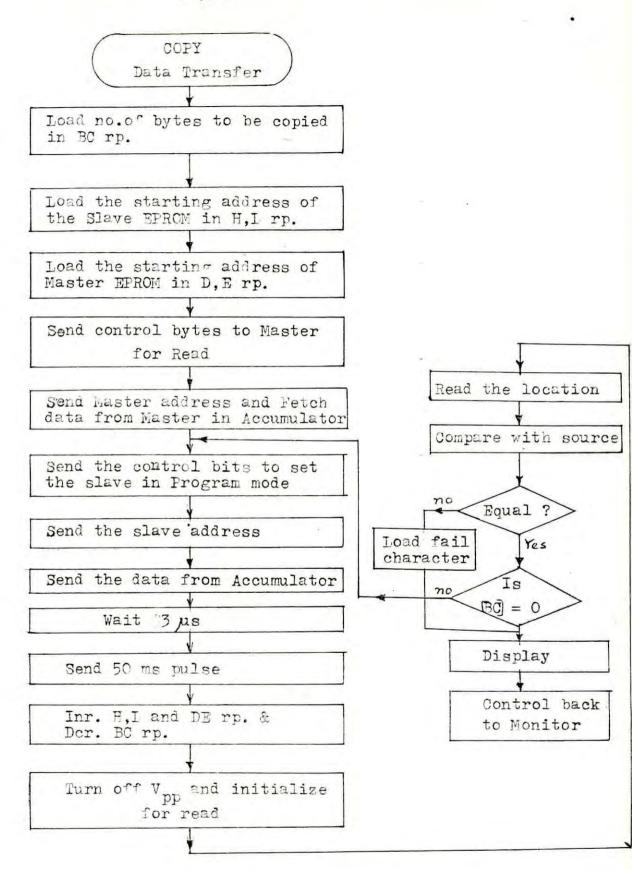


Fig. 7.16(b) Flow Chart for Transfer of Data for COPY.program.

The addresses are to be entered manually from the key board interactively. Here also the next line will appear on the screen only after the previous address is entered with carriage return at the end. The typed address can be corrected using the cursor movement.

The flow chart is shown in Fig.7.15(a) and (b). The first flow chart is for entering the addresses and displaying the Menu and the second flow chart is for fetching the content of Master EPROM and then programming into Slave EPROM and then verifying it.

#### 7.2.8 PRINT Subprogram

This program is used for printing the data from the main memory or from EPROM at Master or Slave location. After the main menu is displayed on the screen, if the key T is pressed, the system will enter the PRINT mode and the PRINT menu as shown in Fig.7.17 will be displayed.

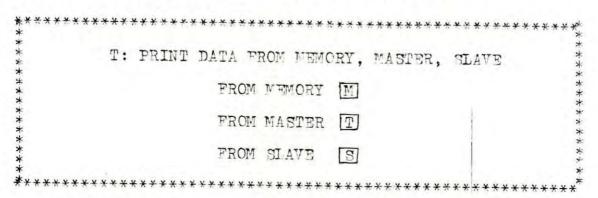


Fig. 7.17 Format of Print Menu

After PRINT Menu is displayed if M is pressed the data from memory will be printed, if T is pressed, data from Master EPROM will be printed and if S is pressed data from Slave EPROM will be printed.

Once the source is selected the microcomputer waits for the start and end addresses of the block of data to be printed. Each of the addresses will be entered interactively. Interaction of the user and the computer for transferring data from Memory is shown in Fig. 7.18(a) and (b). The data is to be entered manually by the user. Next line appears only after the previous line is entered.

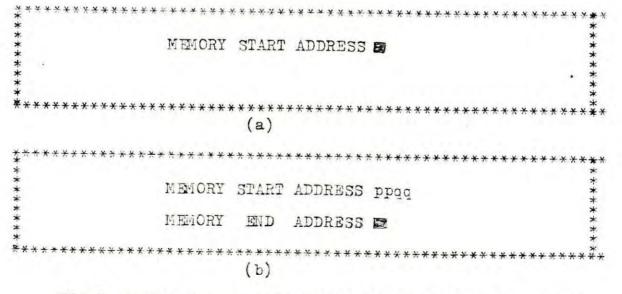


Fig. 7.18 The Interactive Displays of Memory for PRINT.

The flow chart for the PRINT program can also be divided into two blocks.

- 1. Dispalying of Menu and acquisition of address
- 2. Transfering of data to printer.

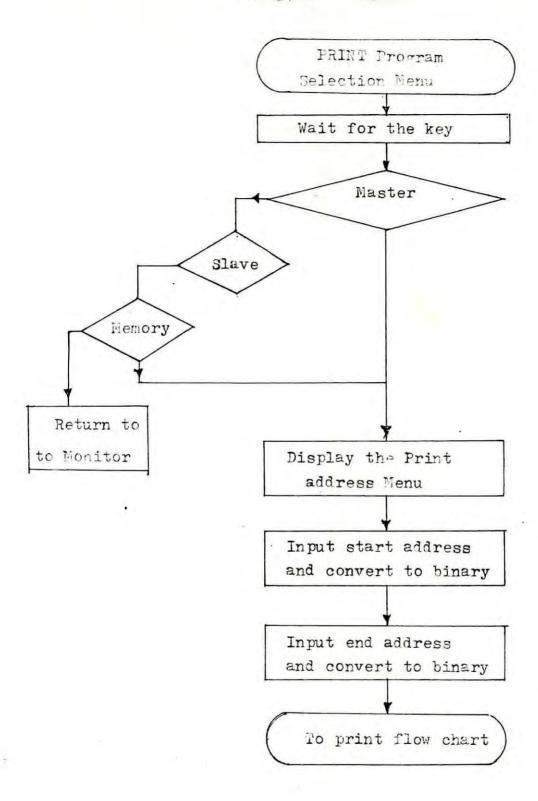


Fig.7.18(a) Flow Chart for Displaying of Print Menu and Acquisition of Address.

The printer is a slow device. So it cannot print data as fast as data can be supplied from memory. To overcome this difficulty the printer has two signals (i) busy (ii) acknowledge. When one byte of data enters the printer, it sends the busy signal indicating that it cannot accept any more data and when printer accepts one byte of data it sends acknowledge signal that it has received data. These signals are examined by the control unit and sends data only when the printer is not busy.

#### CHAPTER - VIII

#### DISCUSSIONS AND CONCLUSIONS

Three buffers, six latches and decoder, NAND gates, inverters were used in the design. A single sided PCB was designed and constructed with in-house facilities. Since the board was single sided as such there was many cross connections, which is very cumbersome. This is due to the unavailability of a PCB laboratory. The design would be easier if integrated chip like 8155 was available. Due to non-availability of the LSI integrated chip, we had to use the simpler type IC's.

This programmer can be used to Program, Verify, Read, Display, Copy and Print. With its 40 output terminals, with proper connections and software any type of EPROM can be programmed.

The designed Programmer can be used for programming Intel 2716, 2732, 2764 and 27128 EPROMs and the EPROMs within Intel 8748, 8049 chips. Since the programmer is software controlled, as such it can be used to program any type of EPROM available, just with a little change in the control program of the EPROM programmer. This programmer will also save the buying of costly manufactured programmer available in the foreign market and it will prove to be helpful in research works on the microcomputer based design.

#### REFERENCE

- 1. Steve Ciarcia, "Build your own Z80 Computer", BYTE Book/A McGraw Hill Fublication/Peterborough, New Hampshire.
- Roger L. Tokheim, "Microprocessor Fundamentals," Schaum's Outline series in computers, McGraw Hill Book Company, New York, 1980.
- 3. Millman J., Halkias C.C., "Integrated Electronics: Analog and digital circuits and systems", McGraw Hill Book Company, New York.
- 4. Givone, D.D., Roesser, R.P., "Microprocessors/Microcomputers:
  An Introduction," McGraw Hill Book Company, New York.
- 5. "Intel Data catalog", 1983.
- 6. Hall, Douglas V., "Microprocessors and digital systems"
  McGraw Hill Book Company, New York.
- 7. "Pro-Log Corporation", M 980, Electronics, July 31,1980.
- 8. "G.P. Industrial Electronics", EP4000, Wireless World,
  April 1983.
- H.Muller, "Simple EPROM Programmer" International Centre for theoretical physics, Technology and Application in physics, 18 April - 13 May, 1983.
- 10. "AIM-65 User's Guide", Rockwell International, 1978.
- 11. H.S.Lynes, "EPROM Programmer", Wireless World, April, May, 1982.

## APPENDIX - A

Soft-ware programme

```
*
   010C START LXI D.GEBCH PUT 44 STAR(*) FROM THE LOCATION GEBC OF MONITOR PUT 44 * AT GEDC OF MONITOR.
   0130
          CALL STAR
         LXI D.0E951H
LXI H.SEL
CALL DSPT
   0140
   0150
                               WRITE SELECTION MENU
FROM E951H LOCATION.
   0160
          LXI D. 0E990H
   0170
   0180
          CALL DASH
                                UNDERLINE BY DASH.
         LXI D.CEA10 H
   0190
                                WRITE
   0200
                                COPY
          CALL DSPT
   0210
         MVI A,3A
STA DEA18H
LXI D,CEA1AH
   0220
   0 230
   0240
                                MASTER
         CALL DMST
CALL TO
SHLD (EA23H
   0250
   0260
                                TO
   0270
   0280
         LXI D.OEA27H
          CALL DSLV
   0290
                                SLAVE
   0300
         MVI A. 3A
  0310
         STA CEA2C
         MVI A,03
STA @ EA2E+
                                 C
   0330
   0340
         LXI D.OEA9D
                                WRITE
   0350
         CALL DPRG
                                PRO GRAM
   0360
         HAE.A IVM
   0380
         LXI D, EA9 AH
         CALL DMEM
CALL TO
SHLD DEAA3H
   0390
                                MEMORY
   0400
  0410
                                TO
   0420
         LXI D. OEAA7H
  0430
         CALL DMST
                                MASTER
  6440
         MVI A, 3A
  0 456
         STA DEAACH
  0455
         MVI A, 10H
STA DEAAEH
LXI D, EB10H
                               P
   0460
  0470
                                WRITE
  0490
         CALL DVER
                                VER IFY
  0500
         MVI A. 3AH
         STA CEBIBH
LXI D.EBIAH
CALL DMS
  C510
  0520
  0530
                                MASTER, SLAVE
  0540
         LXI D.CEB27H
  0.550
         CALL DEPS
                               EFA SED
  0560
         MVI A, 3A
  0570
          STA DEE2CH
  0580
         MVI A.16H
  0 590
         STA 0 EB2EH
         LXI D. EB90H
  0600
                               WRITE
  0610
         CALL DED
        MVI A.3AH
STA GEB98H
  0620
  0630
  O EAG
         LXI D.CEBSAH
  0650
         CALL DMS
                               MASTER. SLAVE
  0660
         HAE.A IVM
  0670
         STA DEBACH
        MVI A.12H
STA DEBAEH
  0680
```

0690

```
0700
          LXI D.OECIDH
                                       WRITE
 0710
          CALL DDIS
                                       DISPLAY
 0720
          HAE.A IVM
 0730
          STA DECI.H
 0740
          LXI D.O ECIAH
 0750
          CALL DMSM
                                       MASTER, SLAVE, MEMORY
          HAE, A IVM
 0760
 6770
          STA DEC2CH
 0780
          MVI A.C4
                                       D
 0790
          STA DECEEH
 0.800
         LXI D.CEC90 H
                                      WRITE
 0810
          CALL DMOV
                                       MUVE
         MVI A.3A
STA DEC98H
LXI D.OEC9AH
 0820
 0830
 0 840
         CALL DMEM
CALL TO
SHLD (ECA3H
 0 850
                                      MEMORY
 0760
 C870
                                       TO
 0880
         LXI D. GECA7H
         CALL DMEM
MVI A.3A
 0890
                                      MEMORY
 0900
 6916
         STA DECACH
         MVI A.C DH
 0920
         STA DECAEH
 0930
 0946
         LXI D.OEC 10 H
                                       WRITE
                                       PRINT
 0950
 0960
         MVI A.3AH
STA DEC18H
 0970
 0980
         LXI D. OECIAH
         CALL DMSM
MVI A,3A
0990
                                      MASTER, SLAVE, MEMORY
 1000
 1010
         STA DEC2CH
1020 MVI A,14

1030 STA GEC2EH

THIS IS THE PORTION OF MAIN MENU WHICH WILL
DETECT WHETHER ANY KEY IS PRESSED. IF ANY KEY
IS PRESSED THE PROGRAM WILL JUMP TO THE SUBPROGRAM
CORRESPONDING TO THE KEY PRESSED.

1040 MMKPRS CALL GF6H MAIN MENU KEY PRESSED
1050 CPI 43H IS KEY C.
                                      MAIN MENU KEY PRESSED
IS KEY 'C'
1060
         JZ COPY
CPI 50H
                                      THEN JUMP TO COPY SUBPRG.
IS IT *P*
JUMP TO PROGRAM SUBPRG.
IS IT *V*
1070
1080
         JZ PROGRAM
1096
         CPI 56H
         JZ VERIFY
CPI 52H
1100
                                       JUMP TO VERIFY SUBPRG.
                                      IS IT 'R'
JUMP TO READ SUBPRG.
IS IT 'D'
JUMP TO DISPLAY SUBPRG.
1110
1120
         JZ READ
1130
         CPI 44H
1140
         JZ DISPLAY
1150
         CPI 54H
                                      IS IT 'T'
1130
                                      JUMP TO PRINT SUBPRG.
         JZ PRINT
1170
        CPI 4DH
1180
        JZ MOVE
                                      JUMP TO MOVE SUBPRG.
1190
         JMP MMKPRS
     READ SUBPROGRAM STARTS FROM HERE.
     IT DISPLAYS THE READ SUB MENU.
1200 READ CALL CLEAR
1210 MVI A,52H
                                      CLEAR MAIN MENU DISPLAY.
                                      WRITE
1220
         STA UE951 H
1230
        HAE.A IVM
1240
        STA
               0E953H
1250
         LXI D.0 E955H
1260
        CALL DRD
                                      READ
        LXI D.UE95AH
1270
        CALL DMS
LXI D.0 E957 H
CALL DEPR
1280
                                      MASTER, SLAVE
1290
1300
                                     EPROM
        ACLL TO
SHLD 0E95DH
1310
1320
                                      TO
        LXI D.0 E961H
CALL DMEM
1340
```

MEMORY

MASTER

M SLAVE S

\*

1350

CALL SEMSD

```
1360 RDMENU CALL OF6H
                                  CHECK FOR READ KEY PRESSED.
                                   IS KEY M THEN
1370 CPI 4DH
                                   JUMP TO RMST
1380
        JZ FMST
                                   IS IT S THEN
        CPI 54H
1390
1400
       JZ RSLV
        CFI 51
                                   IF KEY IS Q THEN RETURN
1410
1420
        JZ START
                                   TO MAIN MENU. OTHERWISE
    O JMP RDMENU REPEAT THE LOOP.
ACQUISITION OF START & END ADDRESSES FOR READ
SUBPRG. AND READING OF DATA FROM MASTER START HERE
1430
1460 RMST LXI D.OEA10H
       CALL SPACE
CALL ESEADD
CALL LMEM3
1470
                                   CLEAR *SELECT EPROM *
                                   ENTER START& END ADDRESS.
1480
                                  WRITE MEMORY
1490
                                ENTER MEMORY START ADDRESS.
LOAD RESULT OF SUBTRACTION
        CALL ETSADD
CALL SUBTR
1500
1510
        MVI A,0 A0 H
DUT OBCH
MVI A.04
OUT OBDH
                                 IN B.C R.P.
SET MASTER IN READ MODE.
1520
1530
1540
1550
                                 SET THE ADH, ADL & CR IN OUTPUT MODE.
1560 CALL DERP
1570 CALL HLRP
1580 MRLOF MOV A.H
1590 DUT 389H
1600 MCV A.L
1610 DUT 38AH
                                  LOAD START ADDR.OF MEM.IN D.E
RP.&THAT DF EPROM IN H.L RP.
                                 SEND HIGH BYTE ADDRESS
                                   SEND LOW BYTE ADDRESS.
1 €20
        IN OBBH
                                 READ DATA IN ACCUMULATOR.
        STAX D
1630
1640
        INX H
       INX D
MCV A.B
DFA C
1650
1660
                                  IF (BC) IS NOT O REPEAT
1€70
        JNZ MRLOP
                                   MASTER READ LOOP (MRLOP) .
1680
1690
        HLT
1700 RSLV LXI D. EA10H
                                   SLAVE READING STARTS HERE.
       CALL SPACE
CALL LSLV1
CALL ESEADD
CALL LMEM3
1710
1720
1730
1740
        CALL ETSADD
CALL SUBTR
1750
1760
       MVI A, 04
OUT DBDH
MVI A, 14H
OUT CBCH
1762
1765
                                  SET THE ADH. ADL . CR IN OUTPUT MODE.
                                  SET SLAVE IN READ MODE
1770
1780
1790 CALL DERP
1800 CALL HLRP
1810 SPLOP MOV A.H
1820 DUT 0 E9H
1830 MCV A.L
1840 DUT 0BAH
1850 LK (DBAH
                                  SET THE STARTING ADDRESS
                                  OF SLAVE & MEMORY
                                  SEND THE HIGH BYTE ADDRESS
                                  SEND LOW BYTE ADDRESS INPUT THE DATA
        IN UBBH
1850
                                  STORE DATA IN MEMORY
1 860
       STAX D
187
        INX H
1680
       INX D
1890
        MUV A.B
1900
       DFA C
                                  IF (BC) IS NOT @ REPEAT
1910
       JNZ SRLOP
                                  SLAVE READ LODP(SRLOP)
1925
       HLI
   DISPLAY SUBPROGRAM STARTS HERE . IT DISPLAYS CONTENT
    OF EPROM AT SLAVE OR MASTER LOCATION ON MONITOR.
1930 DISPLAY CALL CLEAR
                                       CLEAR MAIN MENU
1940
       MVI A.04H
                                 WRITE
       STA DE951H
MVI A.3AH
STA DE953H
1550
1960
1970
```

1980 LXI D. CE955H 1990 CALL DDIS DISPLAY 2000 LXI D.0E9.5DH CALL DMSM 2010 MASTER, SLAVE, MEMDRY MASTER M SLAVE S WRITE MEMORY 2020 CALL SEMSD 2060 CALL LMEM3 MVI A,4DH STA DEB9CH 2340 2350

#

\*

```
2360 DMENU CALL 0F6H
2370 CPI 4DH
2380 JZ DSMST
2390 CPI 53

CHECK FDR DISPLAY KEY PRESSED
IS IT M THEN GO TO
DSMST
IS IT S THEN GO TO
       JZ DSSLV
CPI 52H
                                   DSSLV
2400
                                   IS IT R THEN GO TO
                        DSMEM
2410
       JZ DSMEM
2430 CPI 51 IS IT Q THEN RETURN TO
2440 JZ START MAIN MENU OTHERWISE LOOP BACK
2450 JMP DMENU TO SEARCH FOR KEY PRESSED
2460 DSMST LXI D, DEA10H CLEAR SELECT EPROM*
       CALL ESEADD
CALL SUBTR
MVI A.O ADH
DUT CECH

ENTER ADDRESS
RESLT OF SUBTRACTION IN BC RP.
RESLT OF SUBTRACTION IN BC RP.
2480
2490
2500
2510
       MVI A, 04
OUT 0BDH
CALL HLRP
CALL DSLOP
                                  SET ADH. ADL & CR IN OUT MODE.
2520
2530
                                  START ADDR. IN HL
DISPLAY THE CONTENT
2540
2550
2555
       HLT
2560 DSSLV LXI 0EA10H
2570 CALL SPACE
2580 CALL LSLVI
       CALL ESEADD ENTER ADDRESS CALL SUBTR
2590
2610
       MVI A,04
BUT DBDH
MVI A,14H
BUT DBCH
2620
2630
2640
                                  SET SLAVE IN OUTPUT MODE
2645
       CALL HERP
CALL DSLOP
DISPLAY
2€50
2660
2665
       HLT
2670 DSMEM LXI DEATOH
       CALL SPACE
CALL LMEM1
2€80
2690
       CALL ESEADD ENTER START, END ADDRESSES
CALL SUBTR RESULT OF SUBTRACTION IN B, C RP
LHLD STRT1 , LOAD STARTING ADDRESS IN H, L
2700
2710
2720
2730 DSLOPM MOV A.M
2740
       PUSH B
        MOV B. A
2750
        CALL 103H DISPLAY CONTENT
2760
       PCP B
2770
        INX H
2780
        DCX B
2790
2800
                                   IS IBC I IS NOT 0 THEN
       OFA C
        DFA C IS (BC) IS UNIX DSLOPM LOOP BACK
2710
2820
2830 HLT
    *PROGRAM* SUBPROGRAM STARTS FROM HERE. IT IS USED TO
   PROGRAM AN EPROM AT MASTER OR SLAVE LOCATION
   FREM MAIN MEMORY.
                                        CLEAR MAIN MENU
2890 PROGRAM CALL CLEAR
                                   WRITE
2900 MVI A.16H
2910 STA 0 E951 H
        HAE A. IVM
STA 0 E953 H
2920
2930
       LXI D,0 E9 55H
        CALL DPRG
                                   PROGRAM
2950
        LXI D.DE95DH
2960
                                    MASTER
2970
        CALL DMST
       LXI D.0 E9 65H
2980
2990
       CALL DEPR
                                   EPR CM
2995 LXI D.CE96CH
       LXI H,FRM
CALL DSPT
                                  DISPLAY FROM
2996
2597
```

```
LXI D.0E972H
LXI H.MEM
     2998
     2999
     3000
           CALL DSPT
                                    DISPLAY MEMORY
            CALL LMEM
CALL LSAD
CALL LEAD
CALL ESEADD
     3001
                                 DISPLAY MEMORY AND
START ADDRESS ON SAME LINE
DISPLAY END ADDRESS IN NEXT LINE
ENTER STAPT & END ADDRESSES
DISPLAY MASTER AND
SI ART ADDRESS ON THIRD LINE
ENTER MASTER STAPT ADDRESS
                                     DISPLAY MEMORY AND
     3002
     3005
     3010
     3015
            CALL LMST2
     3020
           CALL LSAD3
     3025
            CALL ETSADD
CALL SUBTR
    3040
    3050 PLCP MVI A.DO
                                  SET EPRUM IN PROGRAM MODE
           OUT DBCH
MVI A.04
OUT DBDH
     3055
     3060
    3070
                                     SET ADL, ADH, CR IN OUT MODE
            CALL DERP
    3080
                                    LOAD PROGRAM START ADDR . DF EPROM
LOAD MEMOPY START ADDR . IN H.L RP
    3090
            CALL HERP
    6100
            MOV A.H
    3110
3120
3130
           DUT 0 B9H
MEV A.L
DUT 0 BAH
                                    SEND HIGH BYTE ADDRESS
                               SEND LOW BYTE ADDRESS
    3135
            NCP
           MVI A.D4
OUT DBCH
    3140
                                    SEND PROGRAMMING PULSE
    3150
                                     SEND PROGRAMMING PULSE
            CALL DELAY
    3180
3190
                                     WAIT 50 MS.
            INX H
    3200
           DCX B
           MVI A.OADH
OUT CBCH
    3220
                                   SET MASTER IN READ MODE .
    3230
    3240
           IN OBSH
                                 INPUT THE PROGRAMMED BYTE.
    3245
           PUSH D
           MCV D.A
    3 250
           MOV A.M
    3260
                                   LOAD ACC. THE BYTE THAT WAS TO BE PROGRAMMED & COMPARE WITH PROGRAMMED
    3270
           CMP D
           JZ PLOP1
JNZ PLOP2
    3280
                                    BYTE . IF EQUAL JUMP TO PLOP1
    3290
                                    OTHERWISE TO PLOP 2
    3300 PLCP1 PUSH B
    3310
           MOV B.M
    3320
           CALL ICEH
                                   DISPLAY PROGRAMMED BYTE
           PCP B
    3330
           PCP D
          MOV A.B
    3340
    3350
           DEA C
                                  IS (BC)=0
    3360
           JNZ PLOP
                                   IF NOT REPEAT LOGP
    3365
          HLT
    3370 PLCP2 PUSH B
    UBEE
          MVI B.FF
   3390
           CALL 103H
                                    DISPLAY FF, LUAD FAIL CHARACTER.
    3400
           PCP B
   3405
          PCP D
   3416
           HLT
SUBROUTINES CALLED BY THE MAIN PROGRAM START FROM HERE. THE FIRST SUBROUTINE IS FOR ENTERING THE ADDRESS MANUALLY FROM KEYBOARD. ONLY FOUR BYTES CAN BE ENTERED AND WRONG ENTRY CAN BE CORRECTED BY CURSOR SHIFTING. NAME OF THIS SUBROUTINE IS *LDADP*
*
4000 LDADE PUSH H
                                    LOAD ADDRESS S.R. STARTS HERE
         PUSH D
   4010
   4020
          PUSH B
   4030
          MVI E.0
   4040
         LXI H. BYTE3
   4050
          MVI D.4
   4060 SP MVI M.20H
                                   MAKE FUUF SPACES AFTER CURSOR.
          DCX H
   4070
   4080
          DCR D
```

\* \* \*

```
4090 JNZ SP
4100 NUM1 CALL OF6H
4110 CPI JDH
                                    IS IT CARRIAGE RETURN.
    4120
           JZ NUM2
           CP1 8
JNZ CHAR
MCV A, E
                                   IS IT BACK SPACE. IF NOT THEN JUMP TO CHAR
    4130
    4140
    4150
           CPI 0
    4160
    4170
           JZ NUM1
    4180
           DCR E
    4190
           DCX H
           MVI B.8
    4200
   4210
4220
           CALL 103H
           JMP NUM1
          CHAR MOV B.A
   4230
                                   SAVE ACCUMULATOR.
           MCV A,E
CPI 4
    4240
    4 250
    4260
           JZ NUM1
           MGV A.B
CPI 30H
   4270
                                 3. IS ASCII CODE FOR 0
IS CHAR. LESS THAN 30H.
    4280
    4290
           JM NUM1
           CPI 3AH
    4300
                                   IS IT LESS THAN 9 THEN
    4310
           JM HEXL
                                    JUMP TO HEXL TO ENTER IT
           CPI 41H
    4320
    4330
           JM NUM1
    4340
           CPI 47H
    4350
           MOV B.A
    4360
    4376 CALL 163H
4380 SUI 37H
4385 HEXH MOV M.A
                                DISPLAY THE NUMBER AND THEN
SUTRACT 37H TO MAKE IT HEX NO.
                                   AND STORE NO. ADDRESSED BY H.L RP
    4390
          INR E
    4400
           INX H
    4410
           JMP NUM1
           MCV B.A
    4420
   4430 HEXL CALL 103H
4440 SUI 30H
4450 JMP HEXH
   4440
   4450
   4460 NUM2 LHLD BYTE1
          MCV A.L
   4470
   4480
           RLC
   4490
          RLC
   4500
          RLC
          RLC
   4510
   4520
                                 FIRST TWO DIGITS ARE STORED AT LOCATION *MEMF!
          ADD H
   4530
          STA MEMRI
   4540
          LHLD BYTE2
   4550
          MOV A.L
   4560
           RLC
   4570
          RLC
   4580
          RLC
   4590
          RLC
   4600
          ADD H
                                 NEXT TWO DIGITS ARE STURED AT
          STA MEMR2
   4610
                                  LOCATION *MEME 21
   4620
          PCP B
          PCP D
   4630
          PCP H
   4640
   4656 BYTE1 DS 2
   4670 EYTE3 DS 1
   4680 MEMRI DS 1
   4690 MEMR2 DS 1
   4700 RET
    SUBTRACT SUBROUTINE- THIS ROUTINE SUBTRACTS
    (STRT1) FROM (END1) & STORES IT IN B, C RP
STRT1 AND END1 ARE STARTING AND ENDING ADDRESSES OF THE
LUCATIONS PESPECTIVELY WHEREFROM DATA TO BE READ OR PROGRAMMED
****************
   4710 SUBTR LHLD END1
   4720
          XCHG
   4730
          LHLC STRT 1
          MCV A.H
   4740
   4750
          SUB D
   4760
          MOV C.A
          MOV A.L
SEB E
   4770
   4780
```

+ \*

```
4790 MCV B. A
   4800
       RET
THIS IS SUBFOUTINE FOR
     SHIFTING DATA FROM TWO MEMORY LOCATION TO D.E RP
***********
  4810 DERP LHLD STRT2
                         STARTING ADDRESS WHERE DATA TO BE
       MOV D.L
   4820
                         SHIFTED OF PROGRAMMED IS LOADED
       MOV E.H
  4830
                         IN D. F RP
  4840
       RET
*
*
     THIS IS SUBROUTINE FOR
     SHIFTING DATA FROM TWO MEMORY LOCATION TO H.L RP
  4 850 HLEP LHLD STRT1
                         STARTING ADDRESS WHEREFROM DATA
TO BE SHIFTED IS LOADED IN H.L RP
       MOV A.L
   4860
  4870
       MCV L.H
  4880
       MOV H.A
  4890
       RET
***************
     SUBROUTINE FOR WRITING START, END ADDRESS & THEN ENTERING
     THE ADDRESS MANUALLY FROM KEYBOARD FOUR DIGITS CAN BE
     ENTERED AND ALSO CORRECTED BY CURSOF SHIFTING
**************
  4900 ESEADD CALL LSADI
                        WRITE START END ADDRESS.
  4510
       LXI H. CEAAOH
       CALL CURSD
CALL LDADR
  4920
                        PLACE CURSOR AT DESIRED POSITION
  4930
                         LOAD ADDRESS
  4932
       LHLD MEMRI
                         SHIFT THE ENTERED ADDRESS
  4935
       SHLD STRT 1
                         TO STRT1
  4940
       CALL LEAD
                         WRITE END ADDRESS
  4950
       LXI H.QEB 20 H
       CALL CURS D
  4960
                        PLACE CURSOR AT POSITION
  4970
       CALL LDADE
       LHLD MEMRI
SHLD ENDI
  4980
                         SHIFT THE ENTERED ADDRESS
  4990
                         TO END1
  5000
       RET
******************
     THIS IS SUBROUTINE FOR ENTERING ADDRESS WHERE DATA TO BE
*
     STORED OF PROGRAMMED
************
  5010 ETSADD CALL LSADS
                        WRITE'START ADDRESS' ON 3RD LINE
  5020
       LXI H, OEBADH
       CALL CURSD
CALL LDARD
LHLD MEMP1
  5030
  5040
  5050
                        TRANSFER THE ENTERED ADDRESS
  5060
       SHLD STRT 2
                        TO STRIZ
  507 u
       RET
************
*
    SUPROUTINE FOR CLEARING THE MAIN MENU
*************
  5080 CLEAR LXI D.00E950H
  5090
       CALL SPACE
  5100
       LXI D. DEA 10 H
  5110
       CALL SPACE
       LXI D. @EA90H
  5120
  5130
       CALL SPACE
       LXI D.OEBIOH
  5140
  5150
       CALL SPACE
  5160
       LXI D.CEBIOH
  5170
       CALL SPACE
  5180
       LXI D. CE90H
  5190
       CALL SPACE
  5200
       LXI D. O ECID H
  5210
       CALL SPACE
  5220
       LXI D. OEC90H
  5230
       CALL SPACE
  5240
       RET
```

```
**************
      THIS IS 'DELAY' SUBROUTINE WHICH MAKES A 50 MILLI SECOND LCCP AT A CLOCK FREQUENCY OF 3 MEGA HERTZ
************
   5242 DELAY PUSH D
   5244
        LXI D.1800H
                            180 CH IS FOR 3 MEGA HERTZ CLOCK
   5246 DLLOF DCX D
   5248
         MEV A.D
   5250
         OFA E
        JNZ DLLOP
PCP D
   5252
                            LOOP 1800H TIMES
   5254
   5256
        RET
FOLLOWING ARE THE SUBROUTINES FOR DISPLAYING DIFFERENT
      WORDS AT PARTICULAR LOCATIONS. LOCATIONS ARE LOADED IN D.E RP USING INSTRUCTION LXI D, ADDR
***********
   5258 LMST1 LXI D. QEA94H
5260 CALL DMST
                           DISPLAY MASTER IN FIRST 1 INF
   5270
         RET
   5280 LMST2 LXI D 0E314H
                          DISPLAY MASTER IN SECOND LINE
   5290
         CALL DMST
   5331 LMEM1 LXI D, 0EA94H
                            DISPLAY MEMORY IN FIRST LINE
   5340
         CALL DMEM
   5350
        RET
   5360 LMEM3 LXI D. QEB94H
                            DISPLAY MEMORY IN SECOND LINE
   5370
         CALL DMEM
   5380
         RET
   5390 LSADI LXI D.OEA9BH
                            DISPLAY START ADDRESS IN
   5400
        LXI H.SAD
                            FIRST LINE
   5410
         CALL DSPT
   5420
        RET
   5430 LEAD LXI D.DEBIBH
                           DISPLAY END AUDRESS .
   5440
        LXI H. EAD
   5450
        CALL DSPT
   5470
        RET
   5480 LSAD3 LXI D, DEB98H
                            DISPLAY 'START ADDRESS' IN
   5490
        LXI H, SAD
                            THIRD LINE
   5500
        CALL DSPT
   5510
        RET
   5520 LSLV1 LXI D. OEA94H
                            DISPLAY * SLAVE • IN FIRST LINE
   5580
        CALL DSLV
   5590
        RET
   5600 LSLV2 LXI D. DEB14H
   5610
        CALL DSLV
   5€20
        RET
**************
     FOLLEWING ARE THE SUBROUTINES FOR DISPLAYING DIFFERENT WORDS AT DIFFERENT LOCATIONS WORDS ARE LOADED IN H.L RP
*
*
     AND LOCATIONS ARE LOADED IN D.E RP.
***************
  5630 DMST LXI H.MST
                            DISPLAY MASTER
  5 F 40
        CALL DSPT
  5650
        RET
  5660 DSLV LXI H.SLV
                           DISPLAY SLAVE
  5670
        CALL DSPT
  5680 RET
  5690 DPRG LXI H,PRG
                          DISPLAY PROGRAM!
  5700
        CALL DSPT
  5710
        RIFT
  5720 DMEM LXI H.MEM
                           DISPLAY MEMORY
  5730
        CALL DSPT
  5740
        RET
  5750
       DVER LXI H.VER
                          DISPLAY VERIFY
  5740
        CALL DSPT
  5750
        RET
  5760
       DMS LX I H. MSE
                           DISPLAY MASTER , SLAVE EPROM!
  5770
        CALL DSPT
  5780
       RET
```

```
5790 DERS LXI H.ERS
                       DISPLAY PROM ERASED
  5800
      CALL DSPT
  5810
      FFT
  5820 DRD LXI H, RD
                       DISPLAY READ
       CALL DSPT
  5830
  5840
       RET
                       LOAD ASCII CODE OF T AND O
      TO MVI L,4FH
  5850
  5860
       MVI H.54H
                       IN H.L RP
  5E70
       RET
  5880 DDIS LXI H.DIS
                       DISPLAY 'DISPLAY'
       CALL ESPT
  5890
  5900
       RET
                      DISPLAY MASTER . SLAVE . MEMORY .
  5910 DMSM LXI H.MSM
       CALL DSPT
  5920
  5930
       RET
  5940
      DMCV LXI H,MCV
                       DISPLAY MOVE
       CALL DSPT
  5950
  5960
       RET
                       DISPLAY PRINT
  5970 DPRT LXI H,PRT
  5980
       CALL DSPT
  5990
       RET
  6000 DEPR LXI H.EPR
                       DISPLAY EPROM
       CALL DSPT
  6010
  6020
       RET
  6030 DSLC LXI H,SLC
                       DISPLAY'SELECT'
       CALL DSPT
  6040
  6050
       RET
SUBROUTINE LOP FOR LOOPING UNTIL CONTENT OF B,C RP IS 0
6066 LOP STAX D
       INX D
  6070
       DCR B
  6080
  6090
       CPI 00
  6100
       RET
  6110
****************
    SUBROUTINE FOR PUTTING 44 STARS(*) IN A LINE
**********
  6120 STAR MVI B.2CH
                       24 IS ASCII CODE FOR *
  6130 LUPI MVI A.2AH
       CALL LOP
  6140
  6150
       JNZ LOP1
  6160
       RET
SUBROUTINE FOR PUTTING 40 SPACES IN A LINE
6170 SPACE MVI B. 28H
  6180 LOP2 MVI A,20H
                       2 H IS ASCII CODE FOR SPACE
       CALL LOP
  6190
  6200
       JNZ LOP2
  6210
       RFT
***************
    SUBROUTINE FOR DISPLAYING 40 DASHES IN A LINE
*******************************
  6220 DASH MVI B, 20H
  6230 LOPS MVI A, 2DH
  6240
       CALL LOP
  6250
       JNZ LOP3
  6260
       RET
    SUBROUTINE FOR MAKING 7 SPACES **********
  6270 SVNSP MVI B. 07H
      LOP4 MVI A.20 H
  528€
       CALL LOP
  6290
  6300
       JNZ LOP4
  6310
       RET
```

```
SUBRUUTINE FOR PLACING CURSUR AT A PARTICULAR LUCATION ADDRESS OF LOCATION IS LOADED IN H.L RP
辛辛芹辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛辛
  6320 CURSD SHLD OFFFEH
  6330
       MVI B. 20H
  6340
       CALL 103H
  6350
       RET
********************************
6360 DSPT MOV A.M
  6379
       CFI DEFH
  6380
       RZ
  €390
       STAX D
  6400
       INX H
  6410
       INX D
  6420
       JMP DSPT
  6430
       RET
SUBROUTINE FOR FETCHING THE CONTENT OF AN EPROM AND
     DISPLAYING IT
6440 DSLOP MOV A. H
       DUT 0 B9H
  6450
                         SEND HIGH BYTE ADDRESS
       MCV A.L
OUT DEAH
  6460
  6470
                         SEND LOW BYTE ADDRESS
  6480
       IN CBBH
                         INPUT THE CONTENT
  6490
       PUSH B
  6500
       MCV B. A
  6510
       CALL 103H
  6520
       PEP B
  6530
       INX H
  6540
       MCV A.B
  6550
       OFA C
  6560
       JNZ DSLOP
  6590
       RET
*****************
    DATA FIELD STARTS FROM HERE. THE BYTES ARE ASCII
CODE OF THE WORD WRITTEN AT THE RIGHT SIDE
*
6700 SAD DW 1314H
                         START ADDRESS
       DW 1112H
DW 1420H
  6710
  6720
  6730
       DW 0104H
  6740
       DW 0412H
  6750
       DW CD13H
  6760
       Dw 1320H
  6770
       DE OFFH
  6780 EAD DW 2020H
                         END ADDRESS
  6790
       DW 050 EH
  6 200
       DW 0420H
  6810
       DW 0404H
       DW 0412H
  6820
       DW 0513H
  6830
  6840
       DW 1320 H
  6850
       DE CFFH
  6860 COP DW 0305H
                         COPY
  6870
       DW 1019H
  6880
       DB OFFH
  6896 FRM DW 0612H
                         FROM
  6900
       DW OFC DH
  6910
       DB OFFH
  6920 MST DW 0 D0 1H
                         MASTER
  6930
       DW 1314H
  6540
       DW 6512H
  6550
       DE OFFH
```

```
6960 SLV DW 130 CH
                             SLAVE
6970
      DW 0116H
6580
          05 20 H
      DW
      DB OFFH
6990
7010
         DW 1205H
                              SELECT
     SLC
          0C0 5H
7020
      DW
7030
          0314H
      DW
      DE OFFH
7040
7050
     PRG DW 1012H
                             PROGRAM
          QFO7H
7066
      DW
7070
      DW
          1201H
7080
          0D 20 H
      DW
7090
      DE OFFH
7100
          DW 150 EH
                             UNT IL
     UTL
7110
      DW
          1429H
      DW OC20H
7120
7130
      DE
         OFFH
          DW 0 D0 5H
7140
                              MEMORY
     MEM
      DW GDOFH
7150
7160
      DW 1219H
7170
      DE OFFH
7180
                             SELECTIUN
                                                  MENU
     SEL
          DW 1220H
          0520H
7190
      DI
7200
      DW
          0C20H
7210
          0520H
      DW
7220
      DW
          0320 H
7230
          14 20 H
      DW
7240
         09 20 H
      DW
7250
      DW OF20H
          0E 20 H
20 20 H
7260
      DW
7270
      DW
      DW ODZOH
7080
          0520 H
7290
      DW
7300
      DW
          0E20H
          1520H
7310
      DW
7320
      DE OFFH
7330
7340
     DIS
         DW 0409H
                              DISPLAY
      DW
          1310H
7350
          0C01H
      DW
7360
      DW
          1920H
      DB OFFH
7370
          DW 160 5H
150 9 H
7380
     VER
                              VER IFY
7390
      DW
7400
      DW
          1209H
7410
      DE OFFH
7420
     EPF
          DW 0510H
                              EPROM
7430
          120FH
      DW
7440
      DW
          0D20 H
7450
      DE OFFH
7460
     ERS DW 0510H
                              ERA SED
7470
      DW.
          0113H
7480
      DW 050 4H
7490
      DE OFFH
7500
     RD DW 1205H
                             READ
7510
      DW
          0104H
7520
      DE OFFH
7530
     MOV DW COCFH
                              MOVE
7540
          1605H
      DW
7550
      DE
          OFFH
7560
     PRT
          DW 1029H
                             PRINT
7570
      Dh 097EH
7580
      DW 1420 H
7590
      DE OFFH
7600
     MS DW ODOIH
7610
      DW 1314H
7620
      DW 0512
7630
      DW 23 13H
7640
      DW OCOIH
```

7650

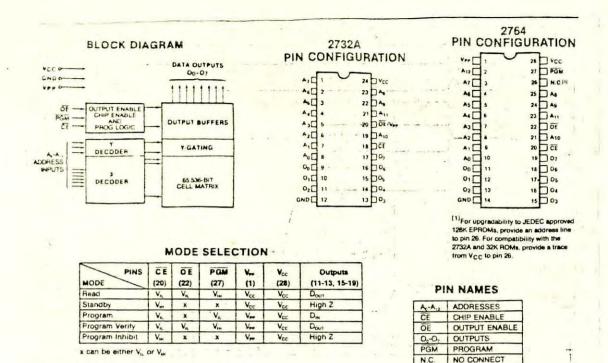
7660

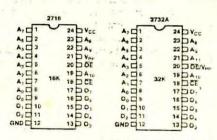
DW 1605H

DE OFFH

#### APPENDIX-B

Pin Diagrams and Programming Waveforms





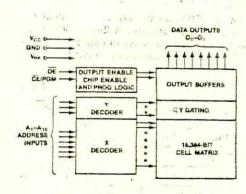
·HMOS is a patented process of Intel Corporation.

Refer to 2732A data sheet for specifications.

#### PIN NAMES

A0-A10	ADDRESSES
CE/PGM	CHIP ENABLE/PROGRAM
ŌE	OUTPUT ENABLE
0,-0,	DUTPUTS

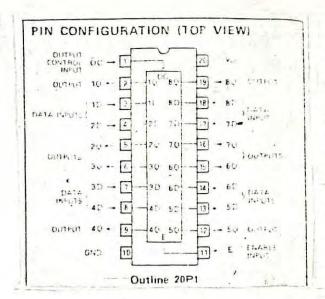
Figure 1. Pin Configuration



see the and a promption of the second

Time Tra

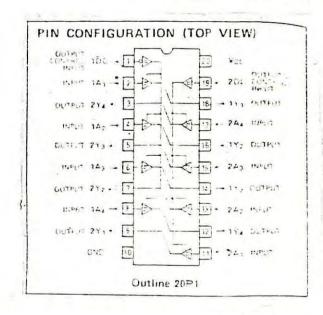
Figure 2. Block Diagram



#### FUNCTIONAL DESCRIPTION

Since the 8 D-type latches use pnp transistor input for the output control input OC and enable input E, which are common to all 8 circuits, the input load factor is small. With a hysteretis of 400mV (typical) specially given to the input circuit E, noise margin is high. When E is high, the information from the data input D appears in the output Q. When the D signal changes, the signal that appears in Q also changes. When E changes from high to low, the status of D immediately before the change is latched. While E is low, the status of Q does not change even if the D is changed. When OC is high, 10 – 80 are all put in the high impedance state Irrespective of other input signals. Since all outputs have high Tan-out, this device is suitable for use as a buffer register, I/O ports or bi-directional bus driver. For application, see M74LS374P.

#### Pin diagram of Intel74LS373.



#### FUNCTIONAL DESCRIPTION

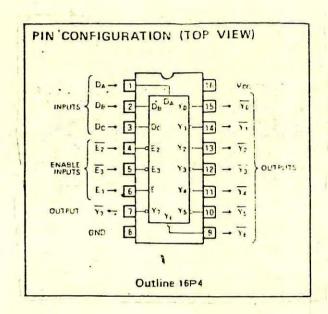
The use of pnp transistors in the input circuit has enabled the achievement of small input load factor. With hysteresis characteristics, the buffer has a 3-state noninverted output with high noise margin.

When output control input  $\overline{OC}$  is low, the output Y is low if input A is low and Y is high if A is high. When  $\overline{OC}$  is high, all of  $Y_1$ ,  $Y_2$ ,  $Y_3$ , and  $Y_4$  are in the high-impedance state, irrespective of the status of A.

By connecting  $1\overline{OC}$  with  $2\overline{OC}$ , it becomes possible to control the output of all 8 circuits simultaneously. Output can be terminated by a load resistor of  $133\Omega$  or over.

For standard characteristics, see M74LS241P.

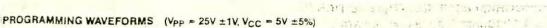
Pin diagram of 74LS244.

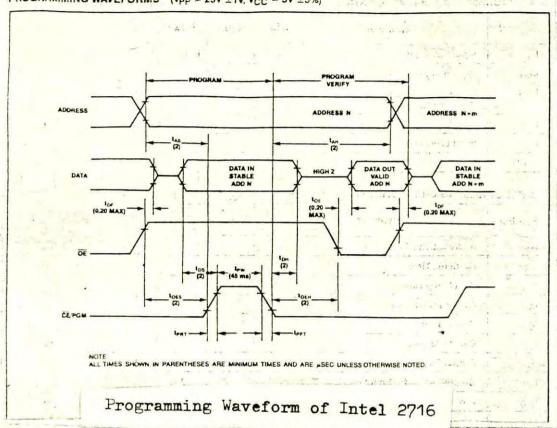


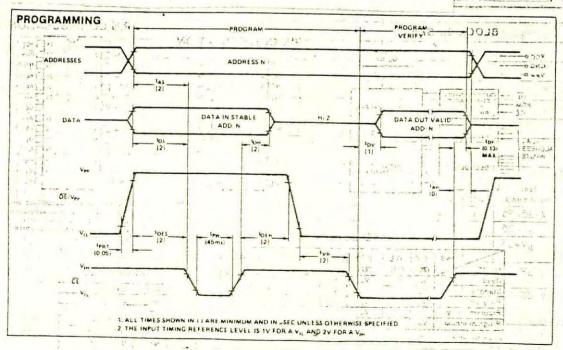
#### FUNCTIONAL DESCRIPTION

For use as a decoder, specify inputs  $D_A$ ,  $D_B$ , and  $D_C$  in 3-bit binary code. In the case of decoding function, the  $E_1$  is kept in high state while  $\overline{E_2}$  and  $\overline{E_3}$  are kept low. If  $E_1$ ,  $\overline{E_2}$  and  $\overline{E_3}$  are not in these conditions, all the outputs become high, irrespective of the status of  $D_A \sim D_C$ . For use as a demultiplexer,  $\overline{E_1}$ ,  $\overline{E_2}$  and  $\overline{E_3}$  are used as data inputs and  $D_A$ ,  $D_B$ , and  $D_C$  as selection inputs. This forms a 1-line to 8-line demultiplexer.

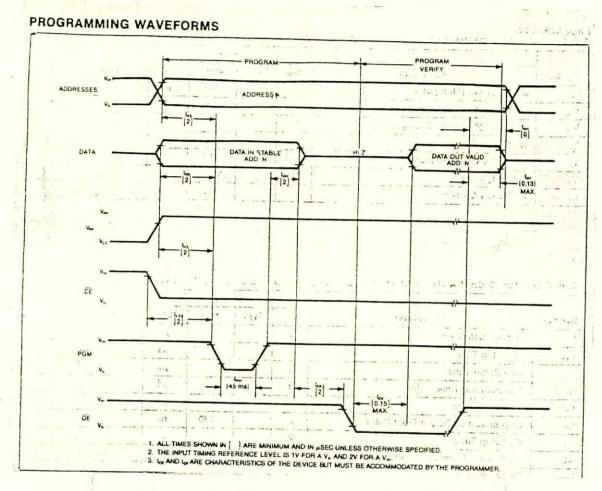
Pin diagram of 74LS138.







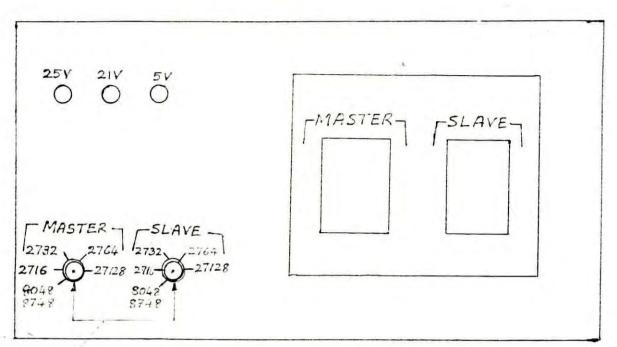
PEDWH.



Programming Waveforms of 2764 &27128.

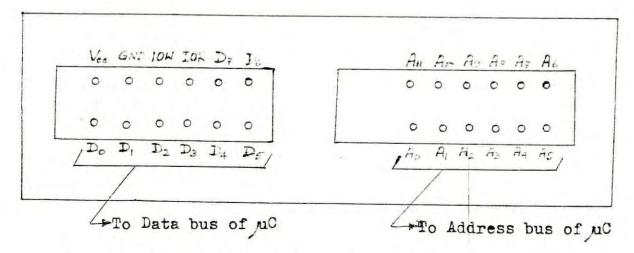
# APPENDIX - C

Printed Circuit Board Designs

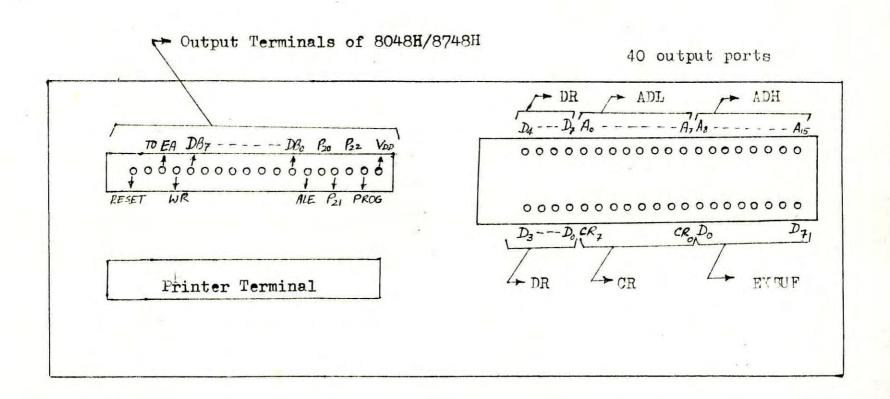


Selection knob for connection to different type of EPROM

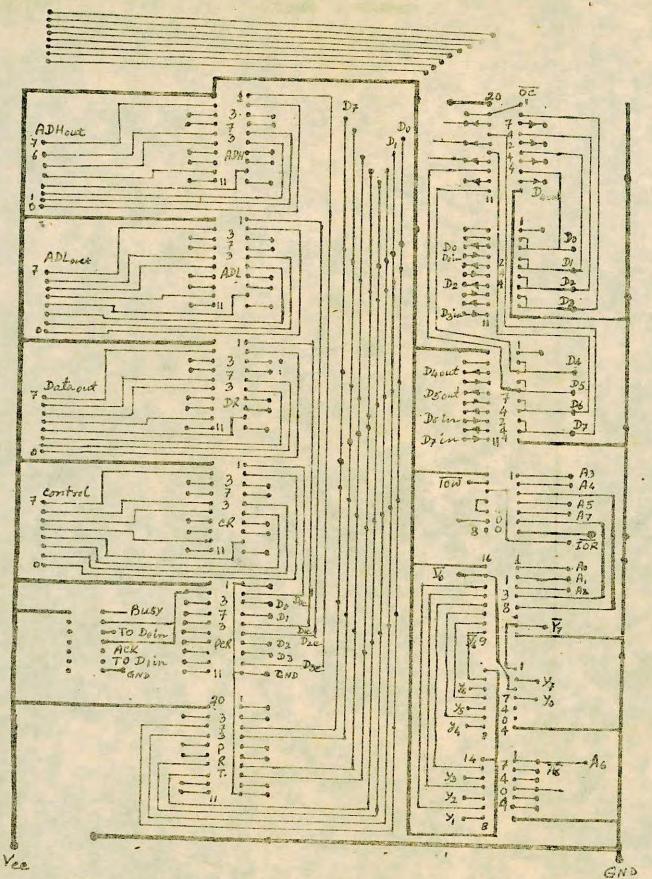
Top side view of the EPROM rogrammer box.(above)



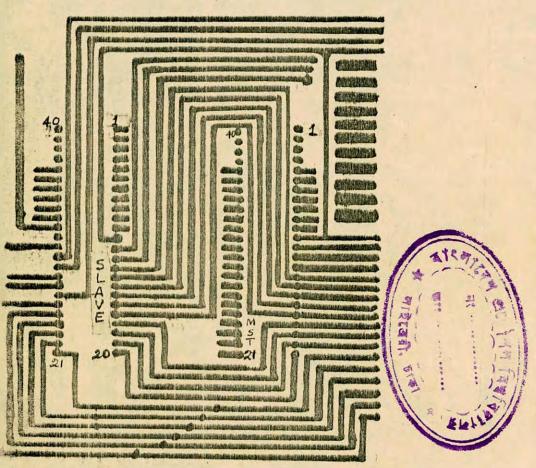
Front view of the EPROM Programmer Box.

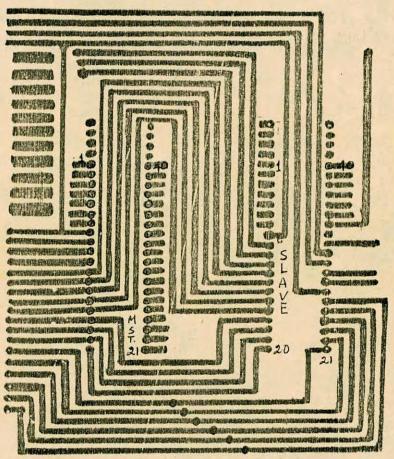


Terminal outputs on the back side



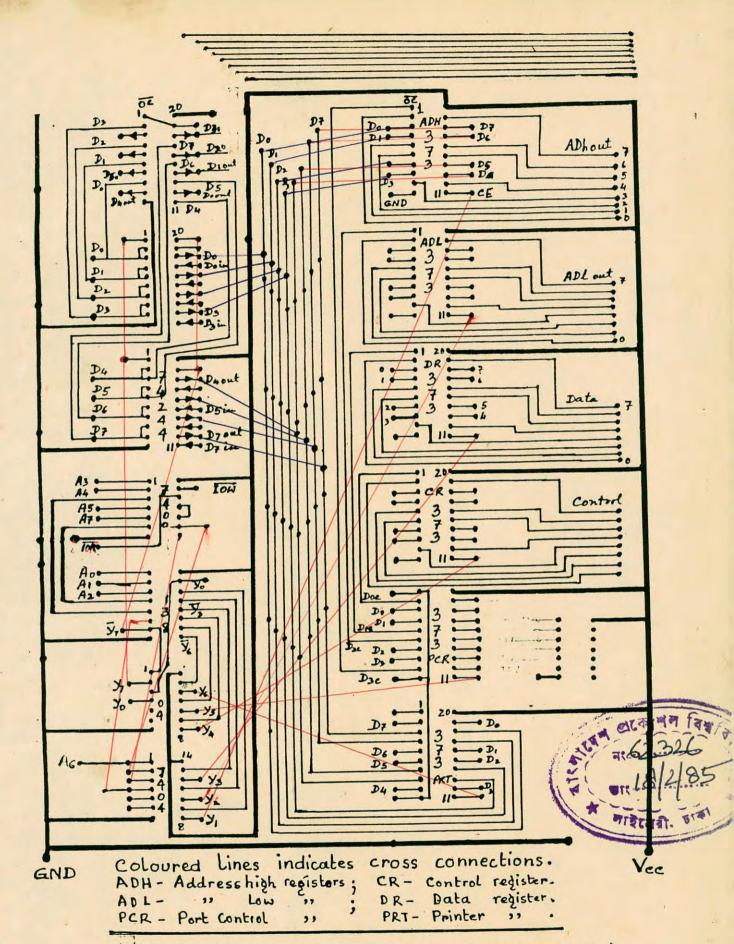
FCB Board design of the Programmer(Reverse side)





FCB of Master & slave connection(Reverse side)

PCB of Master & slave connection(component side)



PCB Board design of the Programmer (component side)